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Gorokhovskiy

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(54) **RECTANGULAR FILTERED VAPOR PLASMA SOURCE AND METHOD OF CONTROLLING VAPOR PLASMA FLOW**

USPC 204/192.38, 298.41, 192.12, 298.11, 204/298.26
See application file for complete search history.

(75) Inventor: **Vladimir Gorokhovskiy**, San Antonio, TX (US)

(56) **References Cited**

(73) Assignee: **Nano-Product Engineering, LLC**, Lafayette, CO (US)

U.S. PATENT DOCUMENTS

(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

This patent is subject to a terminal disclaimer.

3,793,179 A 2/1974 Sablev et al.
3,836,451 A * 9/1974 Snaper 204/298.41

(Continued)

FOREIGN PATENT DOCUMENTS

WO WO 00/62327 10/2000

OTHER PUBLICATIONS

P.Robinson and A. Matthews, Characteristics of a Dual Purpose Cathodic ARC/Magnetron Sputtering System, Surface and Coatings Technology, pp. 288-298, Elsevier Sequoia, Printed in the Netherlands.

(Continued)

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Related U.S. Application Data

(63) Continuation of application No. 10/572,120, filed as application No. PCT/US2004/030603 on Sep. 17, 2004, now abandoned, which is a continuation-in-part of application No. 10/667,279, filed on Sep. 18, 2003, now Pat. No. 6,929,727.

Primary Examiner — Rodney McDonald

(74) *Attorney, Agent, or Firm* — Lathrop & Gage LLP

(51) **Int. Cl.**

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C23C 14/06 (2006.01)
C23C 14/32 (2006.01)

(57) **ABSTRACT**

The invention provides an arc coating apparatus having a steering magnetic field source comprising steering conductors (62, 64, 66, 68) disposed along the short sides (32c, 32d) of a rectangular target (32) behind the target, and a magnetic focusing system disposed along the long sides (32a, 32b) of the target (32) in front of the target which confines the flow of plasma between magnetic fields generated on opposite long sides (32a, 32b) of the target (32). The plasma focusing system can be used to deflect the plasma flow off of the working axis of the cathode. Each steering conductor (62, 64, 66, 68) can be controlled independently. In a further embodiment, electrically independent steering conductors (62, 64, 66, 68) are disposed along opposite long sides (32a, 32b) of the cathode plate (32), and by selectively varying a current through one conductor, the path of the arc spot shifts to widen the erosion corridor. The invention also provides a plurality of internal anodes, and optionally a surrounding anode for deflecting the plasma flow.

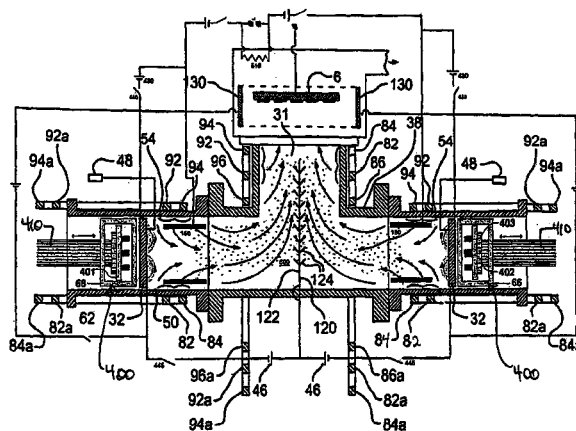
(52) **U.S. Cl.**

CPC **H01J 37/32055** (2013.01); **C23C 14/0605** (2013.01); **C23C 14/0641** (2013.01);
(Continued)

(58) **Field of Classification Search**

CPC C23C 14/0605; C23C 14/0641; C23C 14/0647; C23C 14/325; H01J 37/32055; H01J 37/32614; H01J 37/32623; H01J 37/3266

21 Claims, 26 Drawing Sheets



(52) **U.S. Cl.**
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 (2013.01); *H01J 37/3266* (2013.01); *H01J*
37/32614 (2013.01); *H01J 37/32623* (2013.01)

(56) **References Cited**

U.S. PATENT DOCUMENTS

4,448,659 A 5/1984 Morrison, Jr.
 4,673,477 A 6/1987 Ramalingam et al.
 4,724,058 A 2/1988 Morrison, Jr.
 5,160,595 A * 11/1992 Hauzer et al. 204/192.38
 5,435,900 A 7/1995 Gorokhovskiy
 5,480,527 A 1/1996 Welty
 5,580,429 A * 12/1996 Chan et al. 204/192.38
 5,587,207 A 12/1996 Gorokhovskiy

5,690,796 A * 11/1997 DuPont et al. 204/192.16
 5,840,163 A 11/1998 Welty
 5,997,705 A 12/1999 Welty
 6,645,354 B1 11/2003 Gorokhovskiy
 6,663,755 B2 12/2003 Gorokhovskiy
 6,730,196 B2 5/2004 Wang et al.
 6,758,949 B2 7/2004 Wang et al.
 6,929,727 B2 8/2005 Gorokhovskiy
 2003/0094362 A1 * 5/2003 Gstoehl et al. 204/192.12

OTHER PUBLICATIONS

B.Window and N. Savvides, Charged Particle Fluxes From Planar
 Magnetron Sputtering Sources, J.Vac.Sci. Technol.A 4 (2), Mar./Apr.
 1986, pp. 196-202, 1986 American Vacuum Society.

* cited by examiner

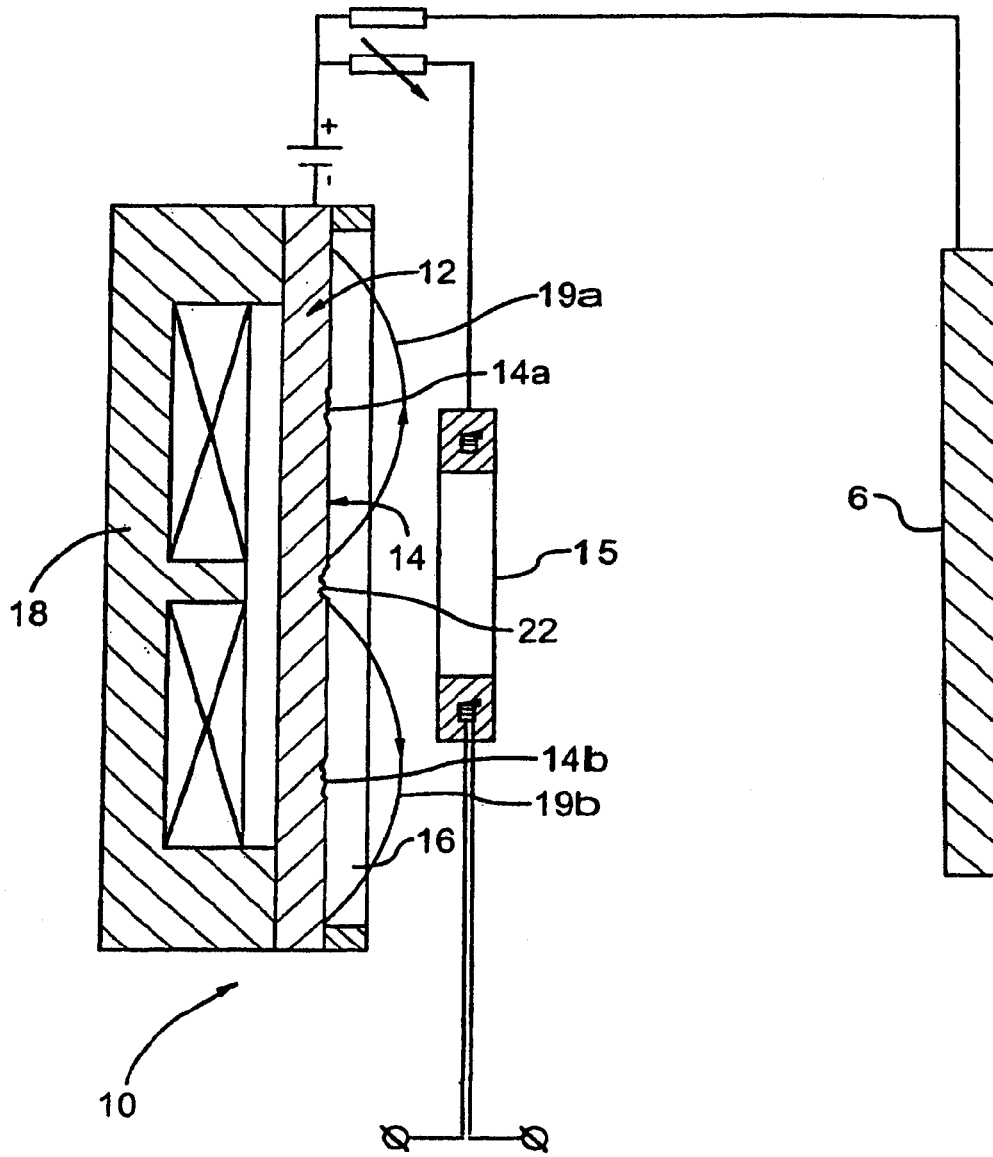


FIG. 1

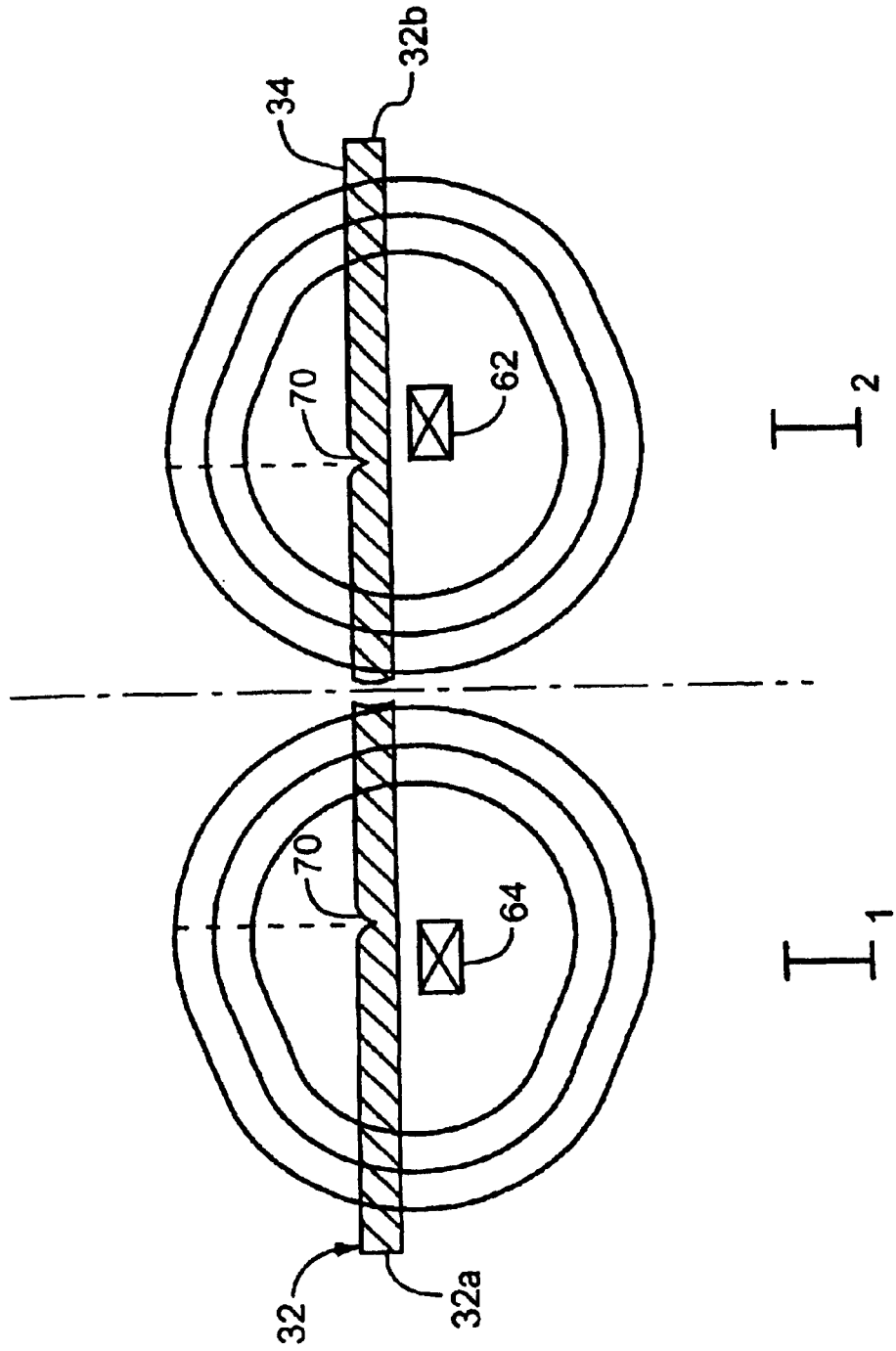
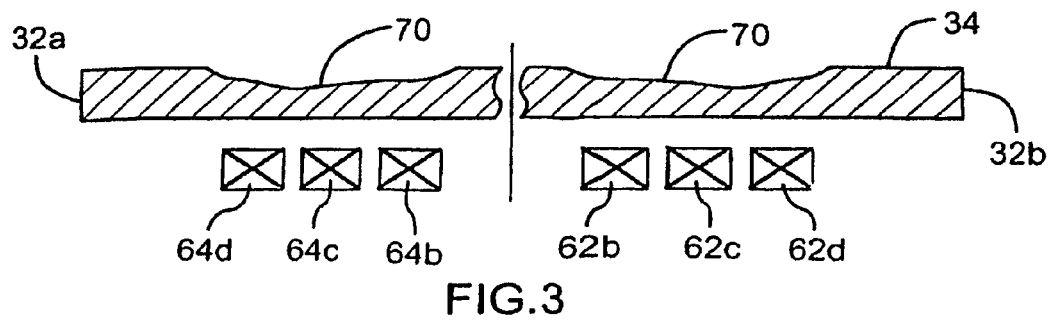
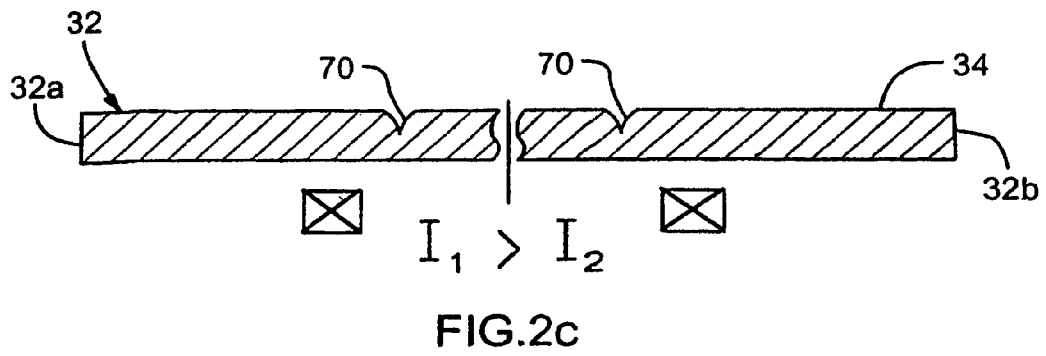
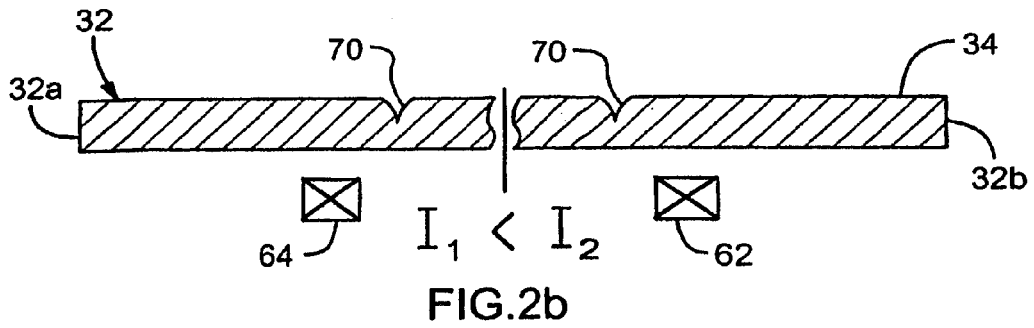


FIG.2a



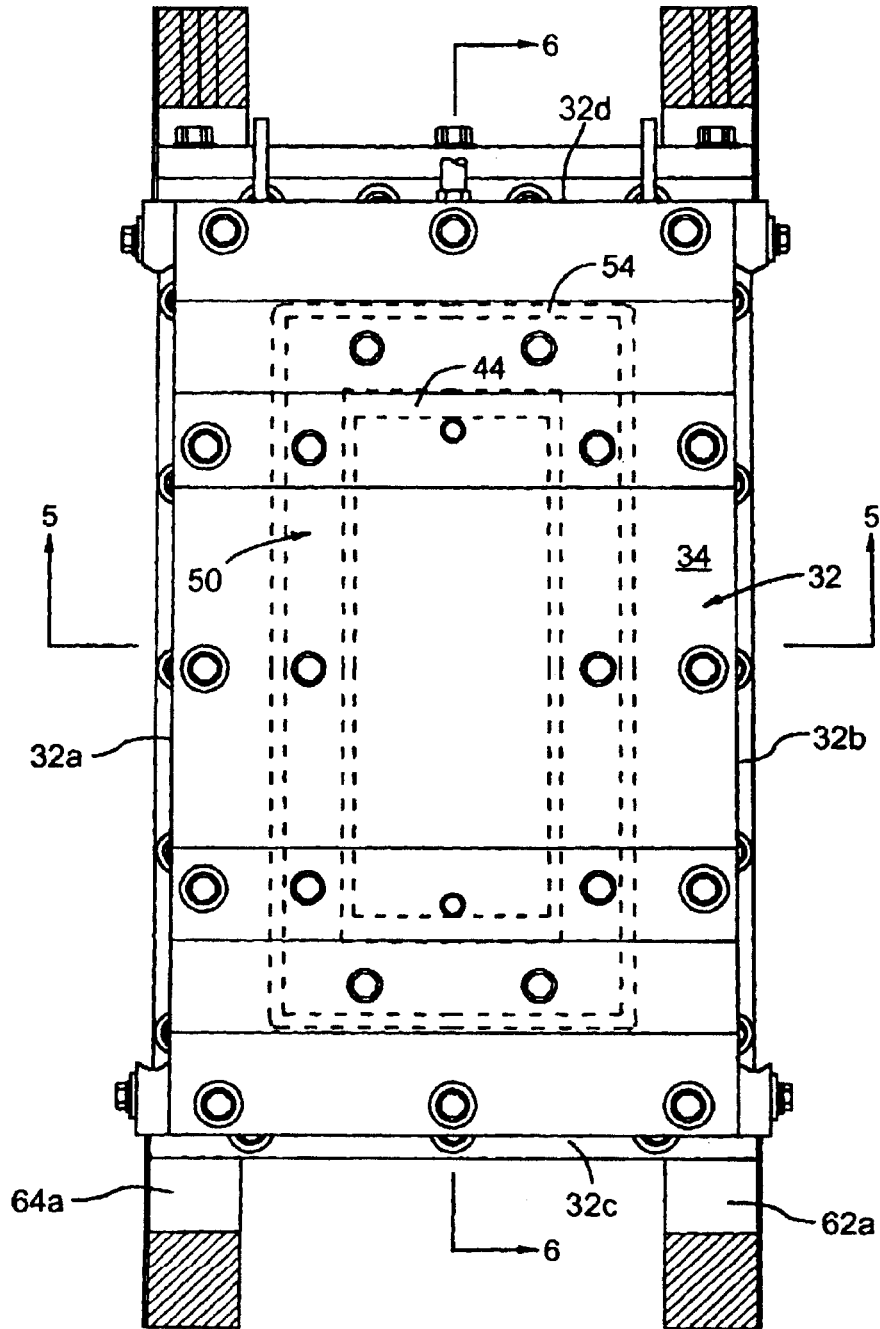


FIG. 4

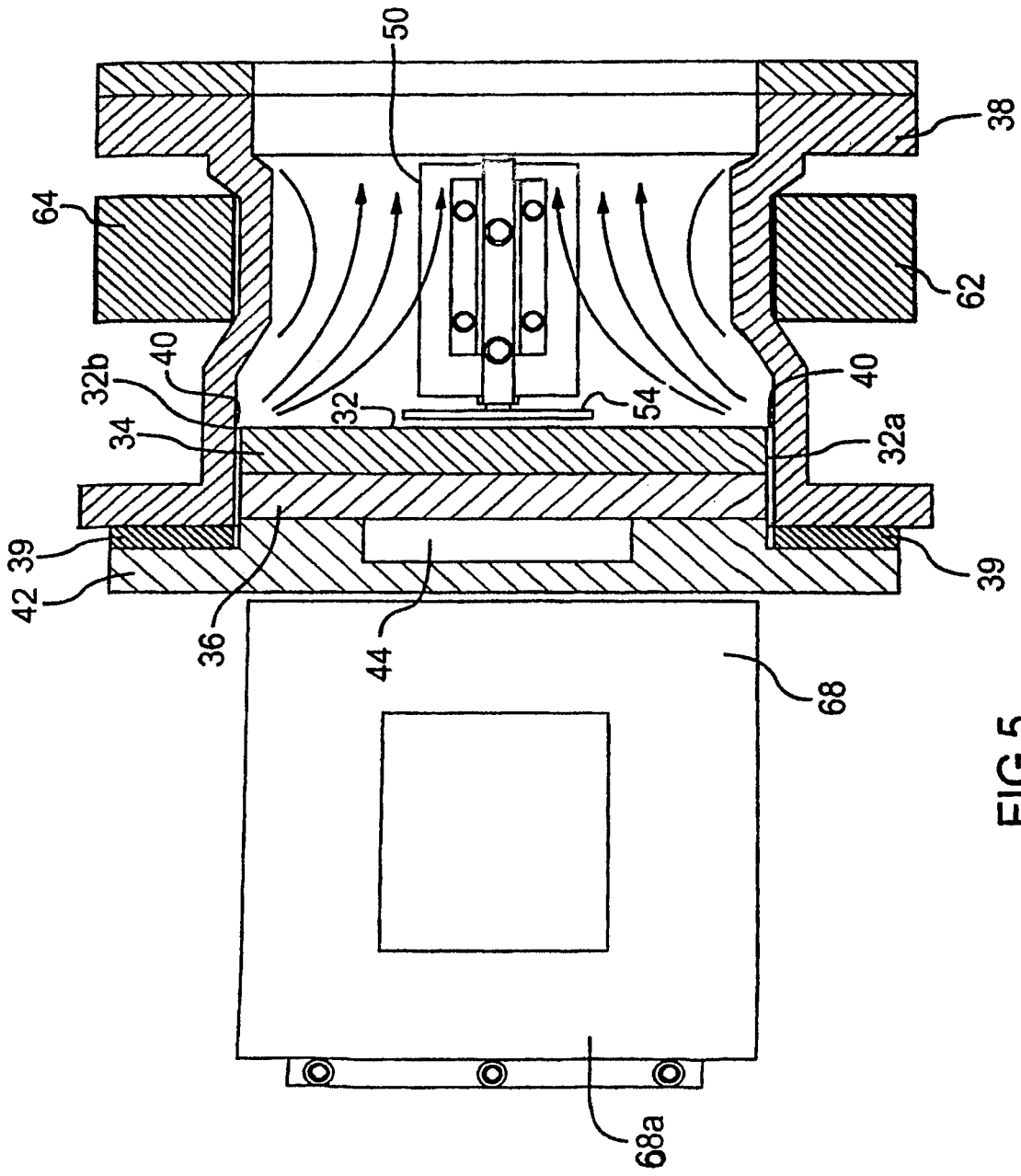


FIG.5

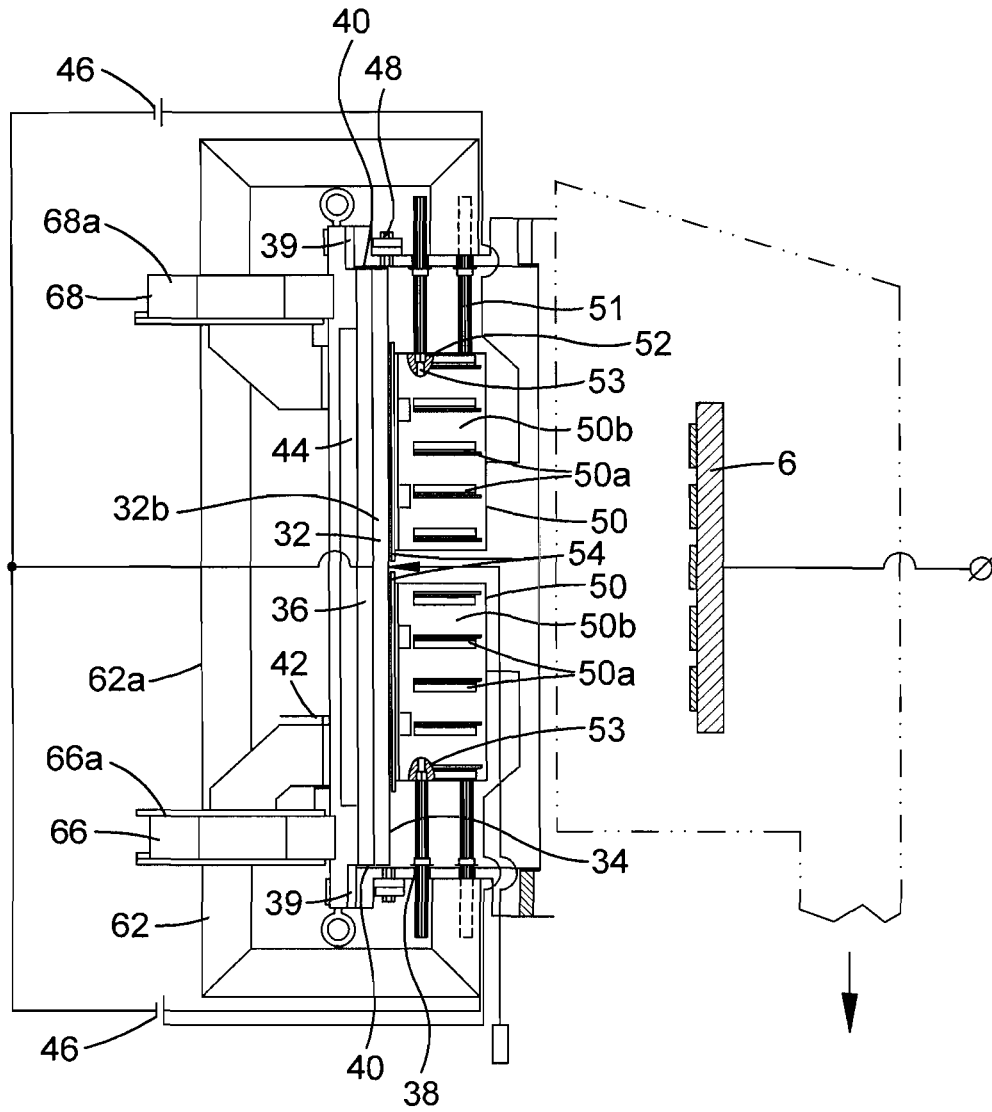


FIG. 6a

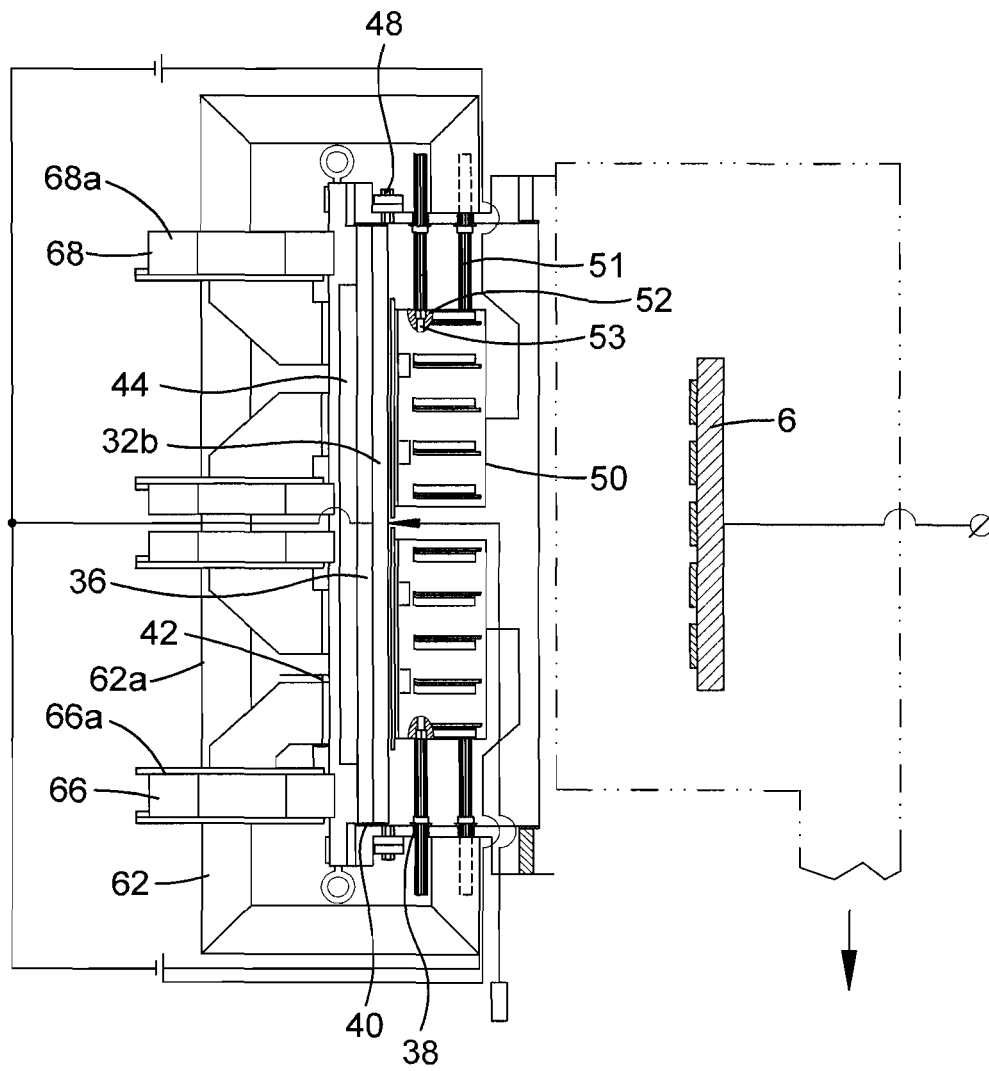


FIG. 6b

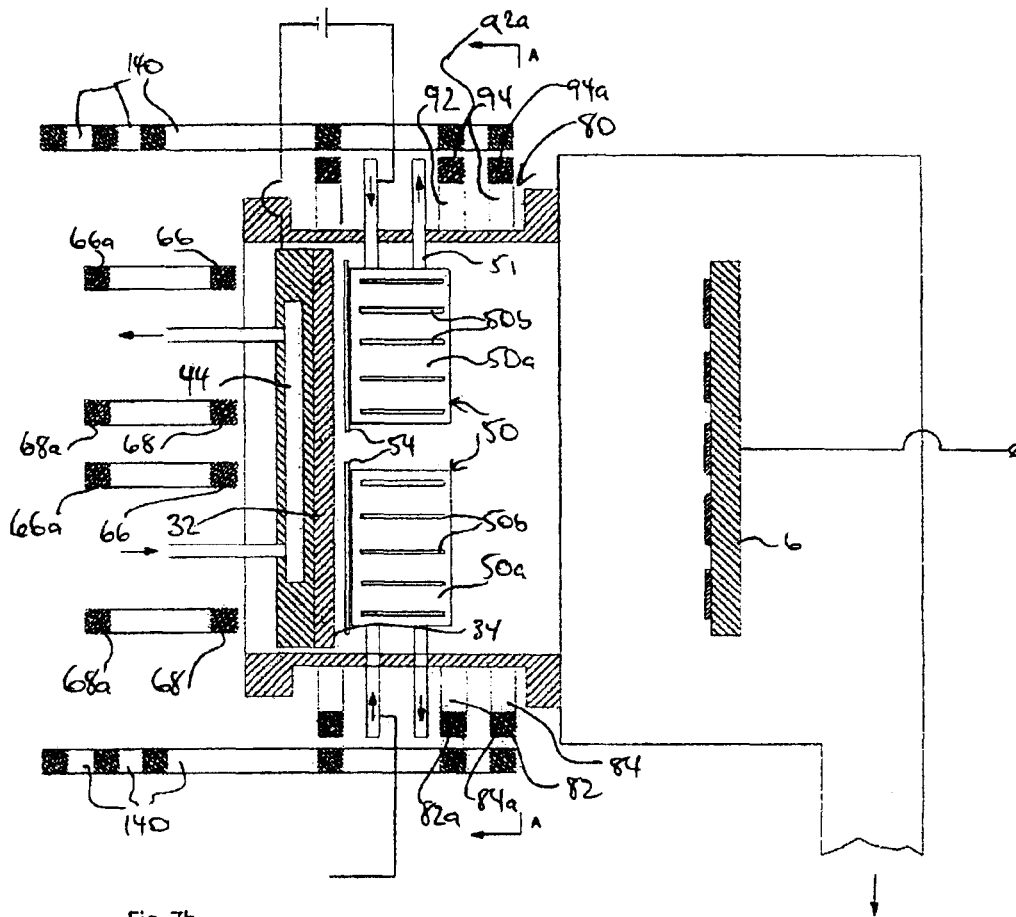
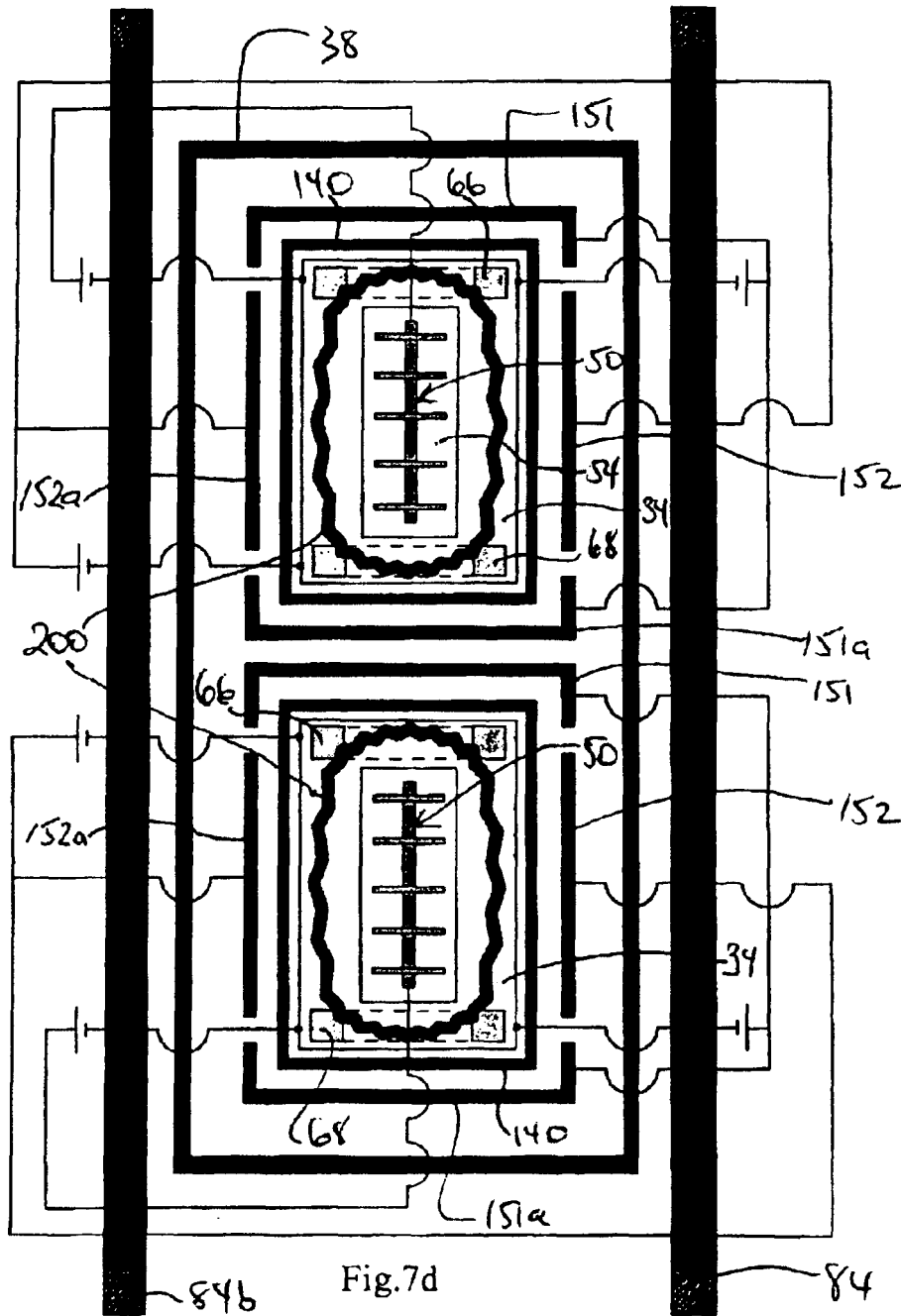


Fig. 7b



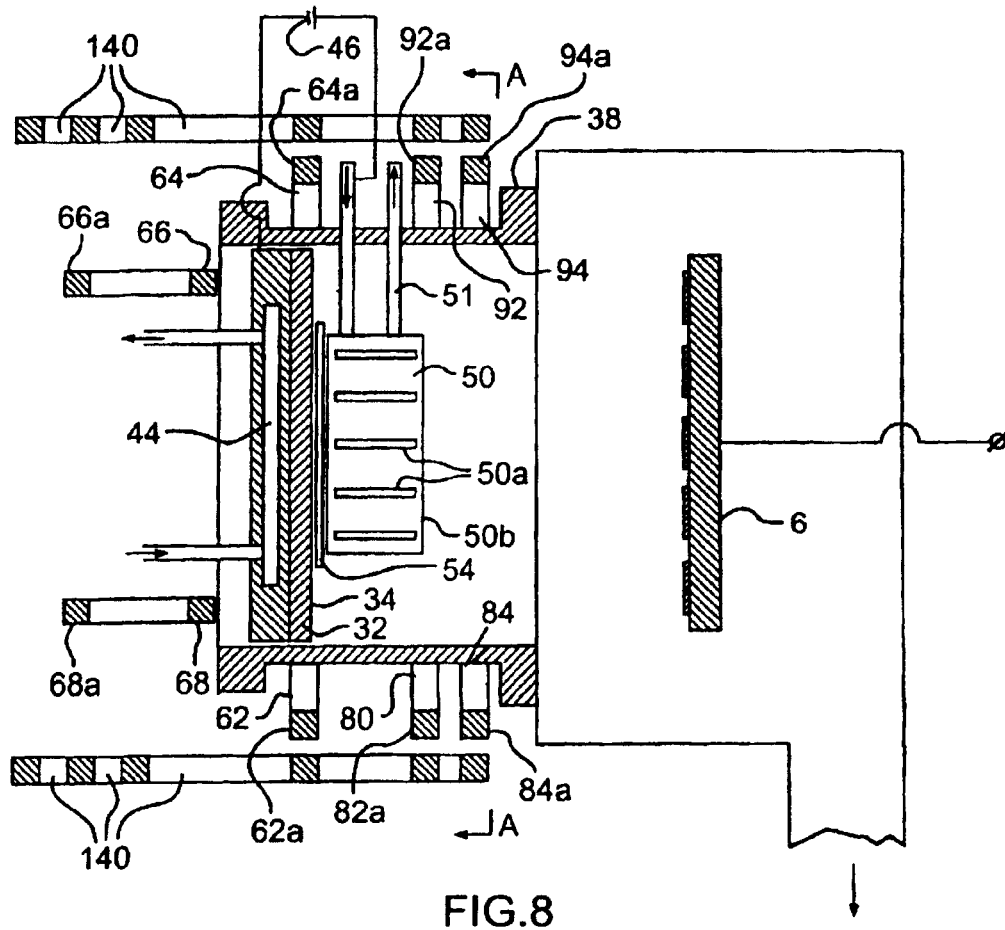


FIG. 8

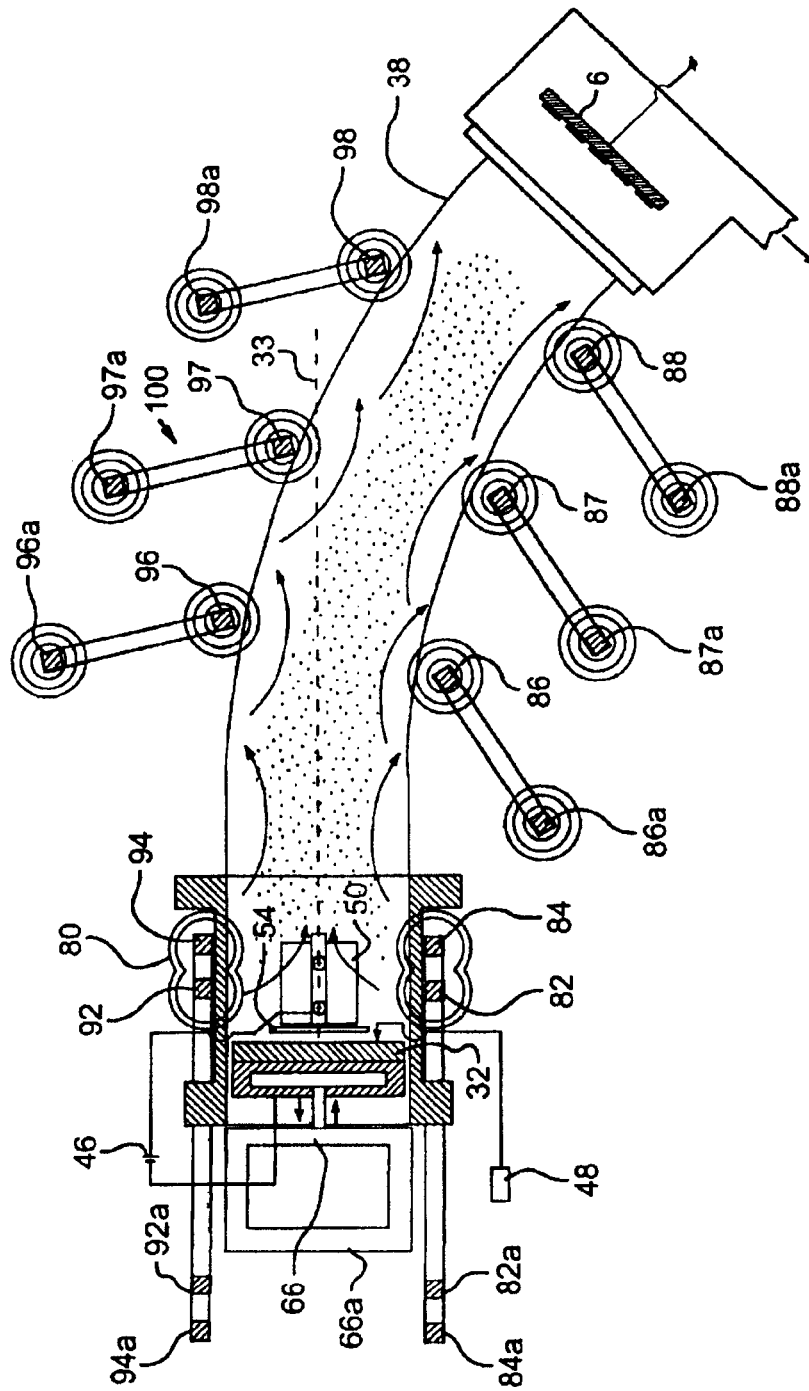


FIG. 9

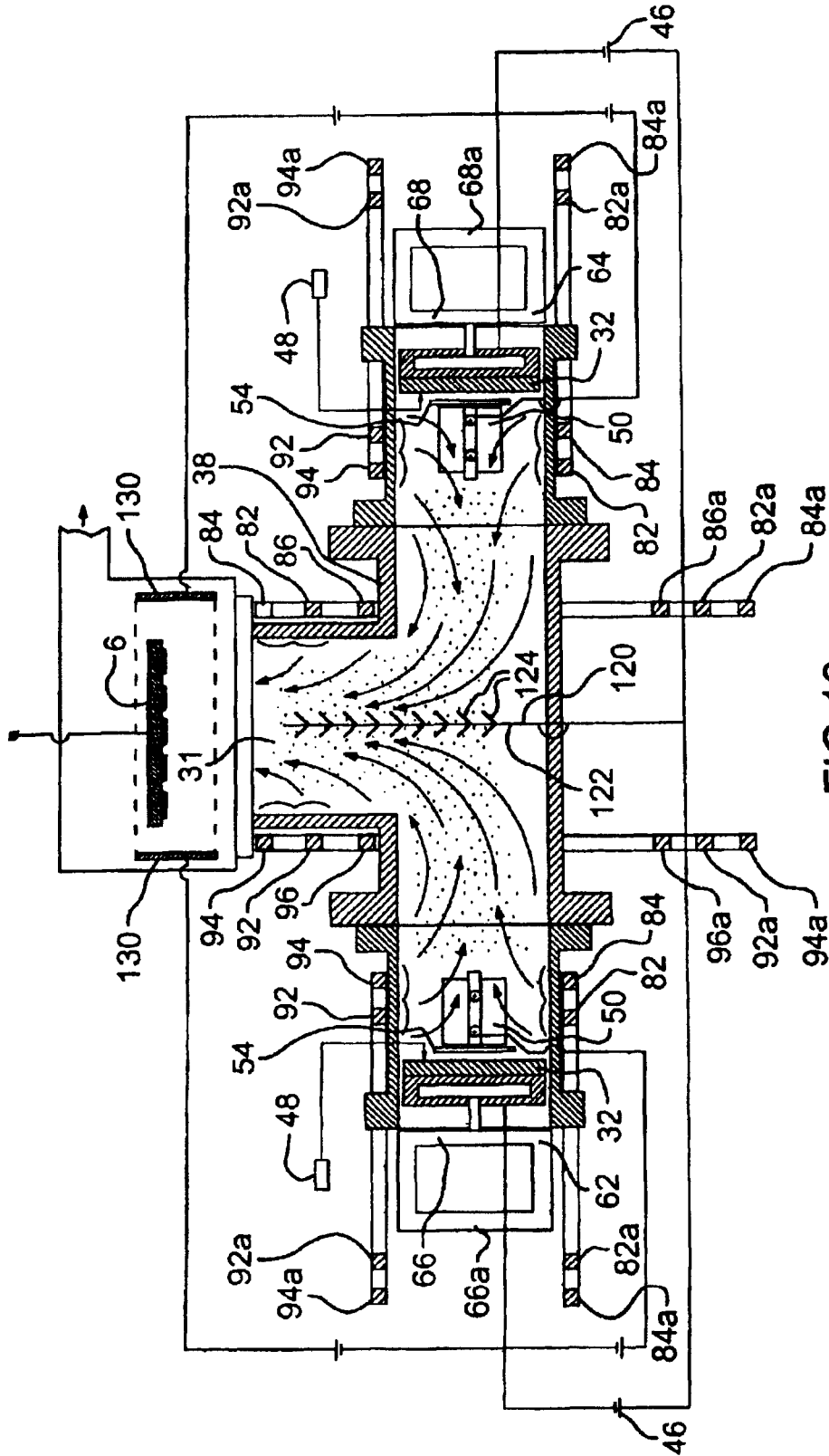


FIG. 10a

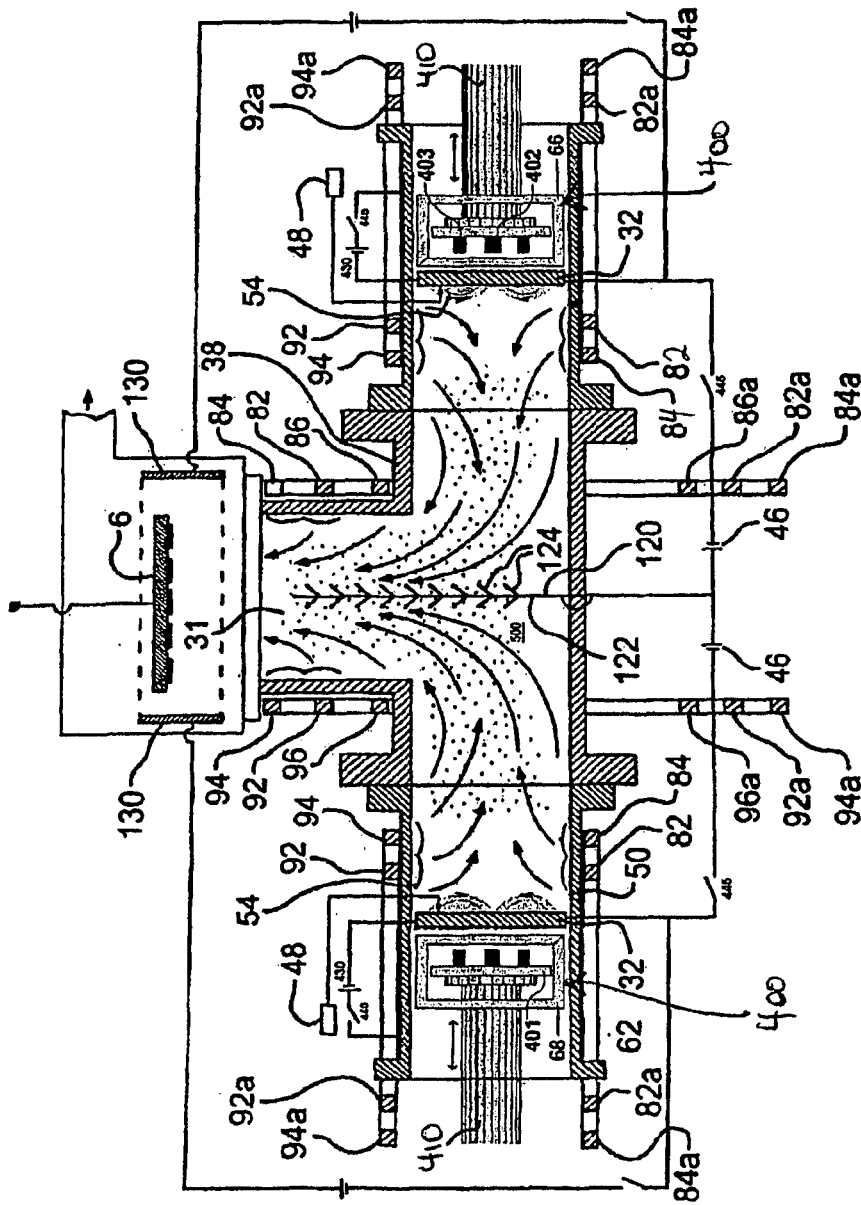


Fig. 10b

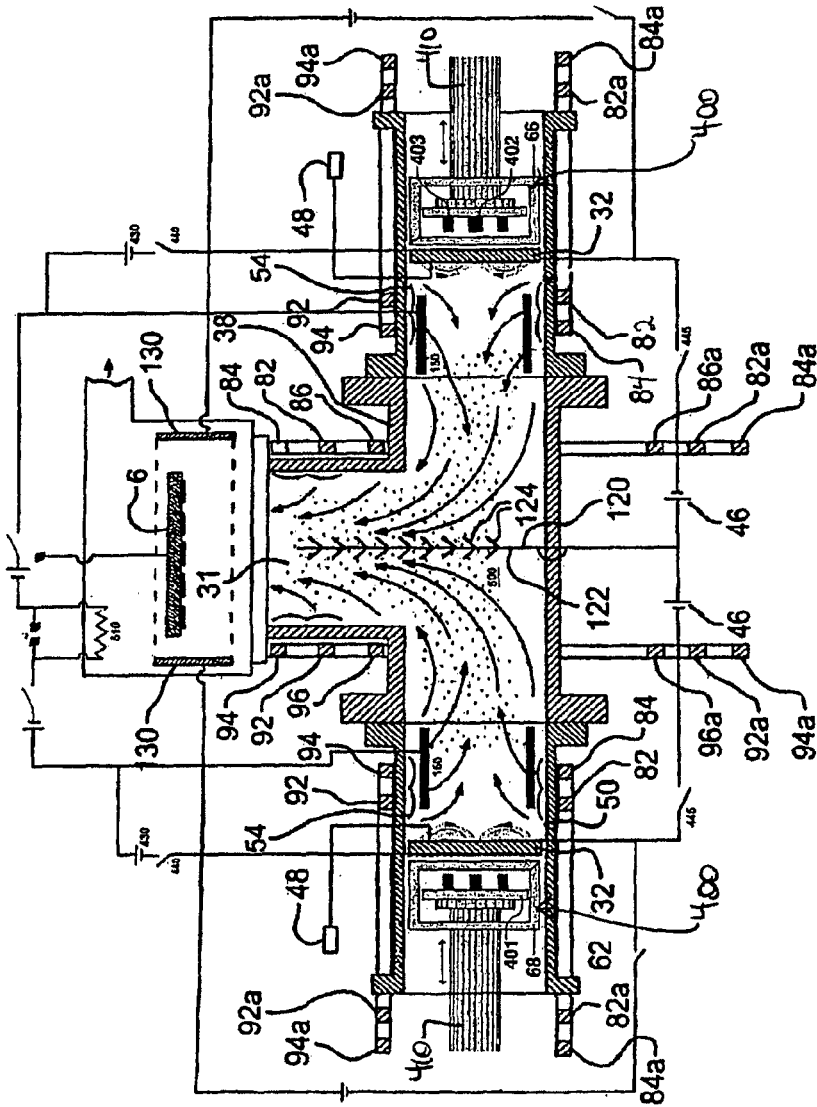


Fig. 10c

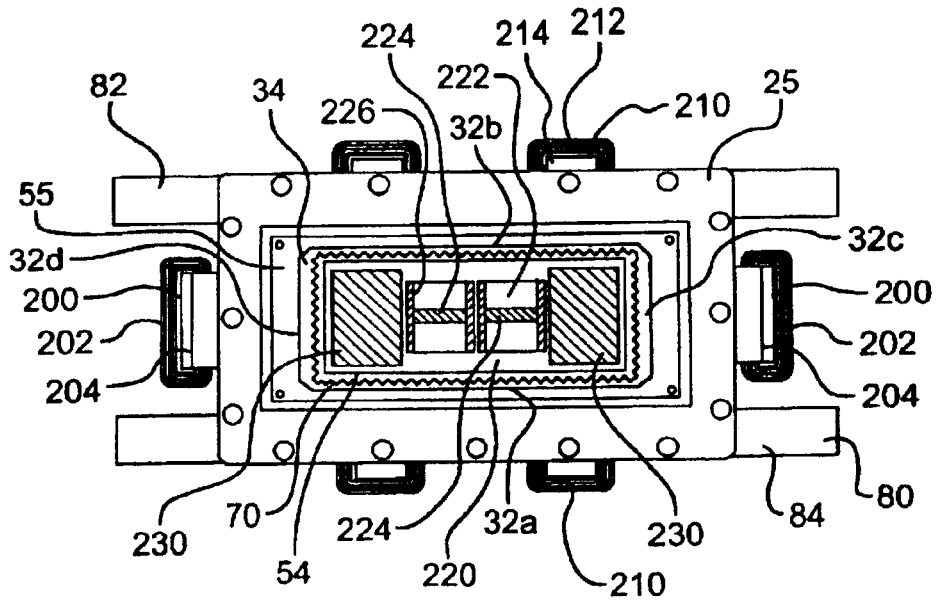


FIG. 12

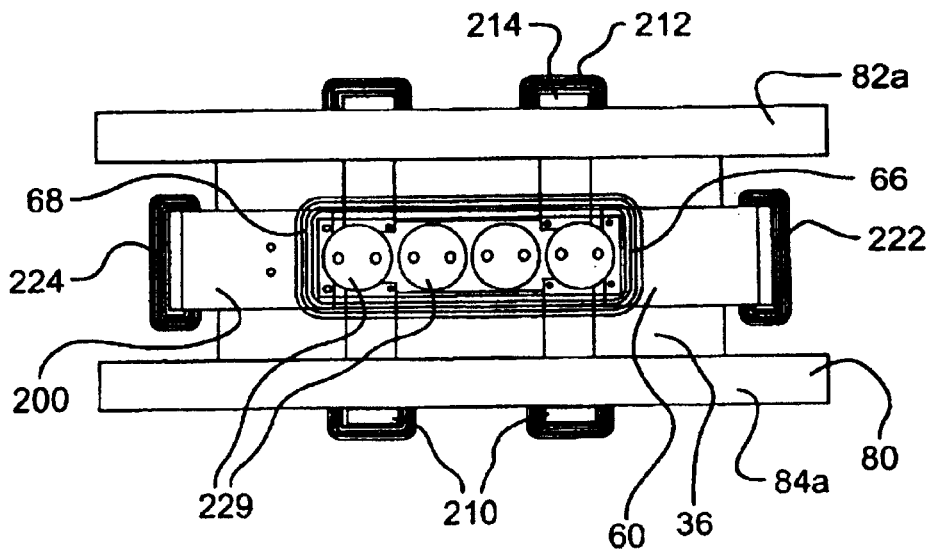


FIG. 13

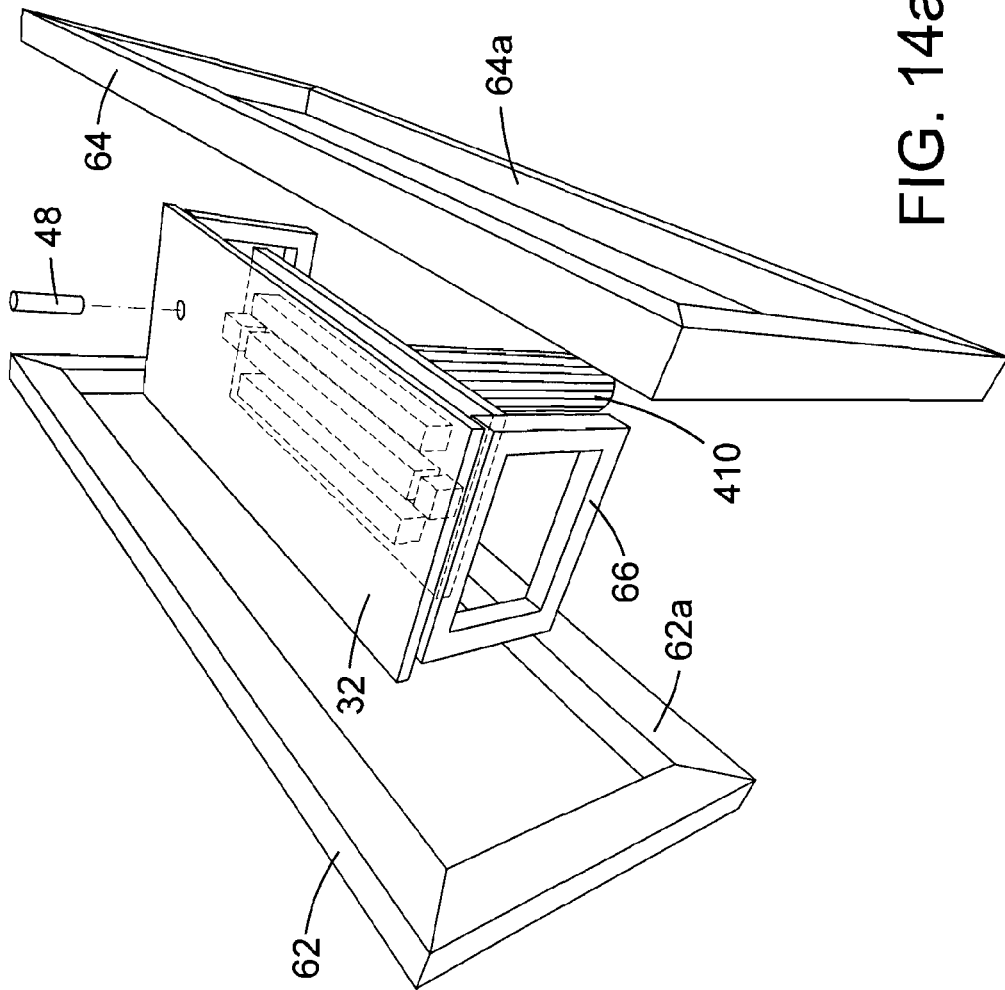
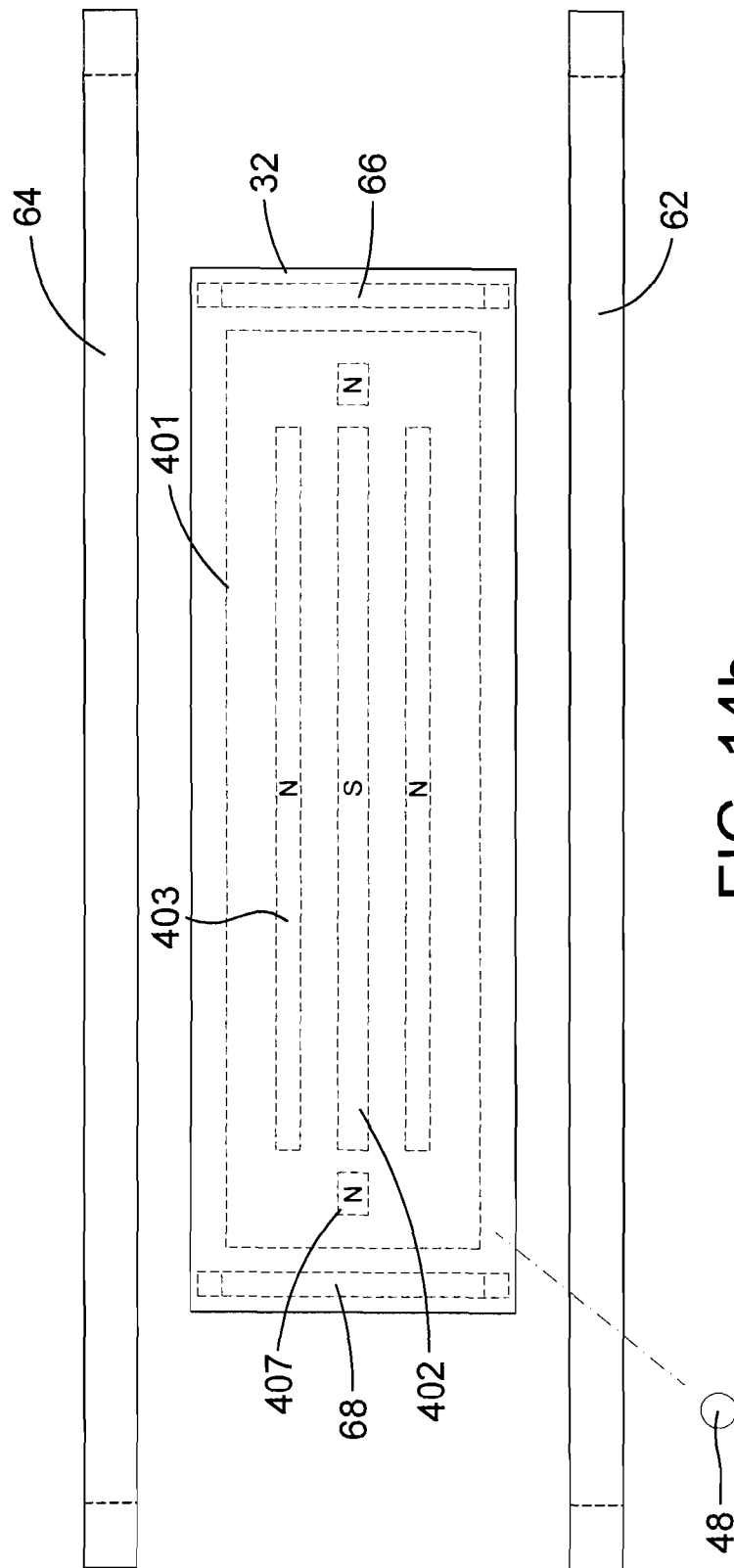


FIG. 14a



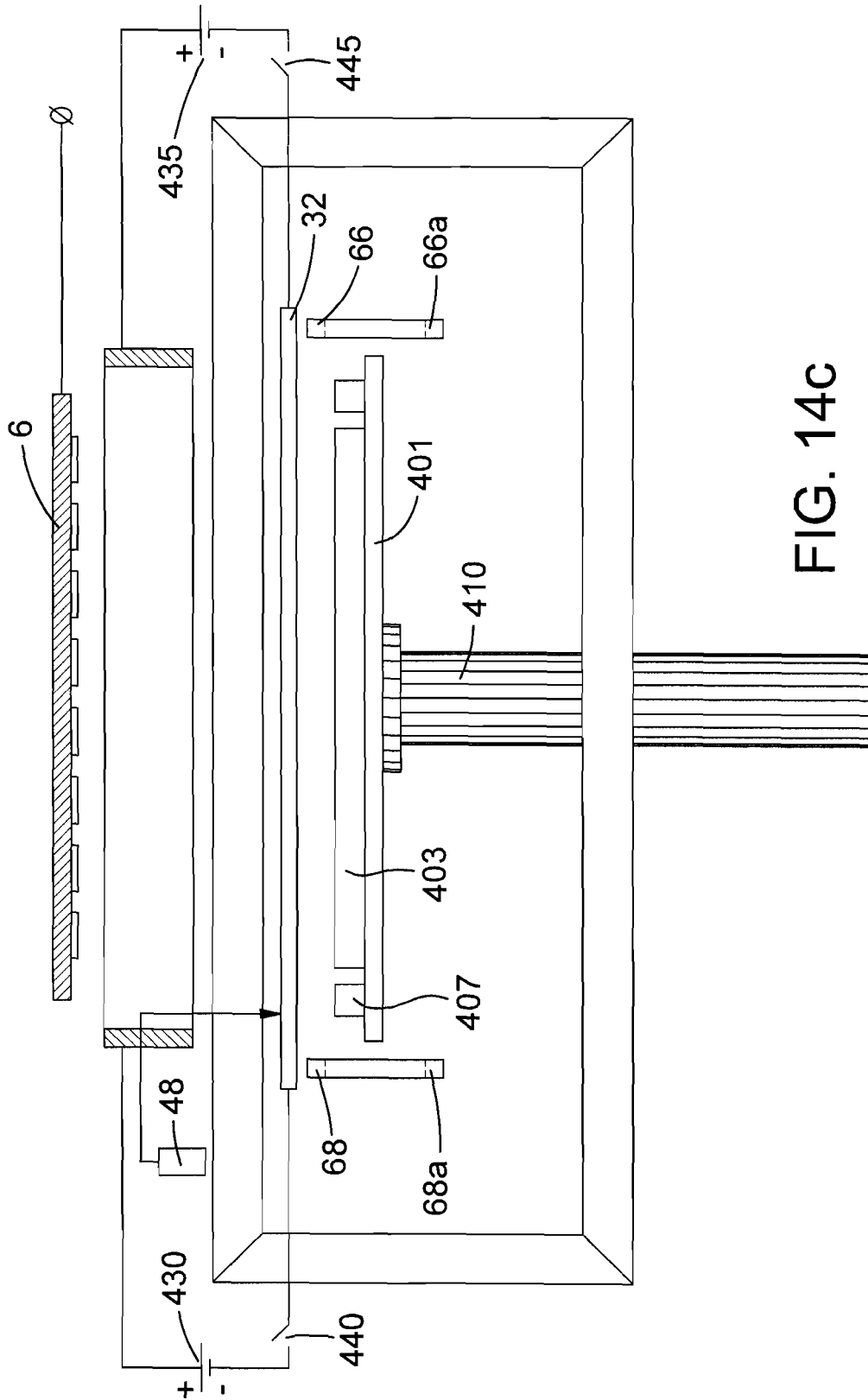


FIG. 14C

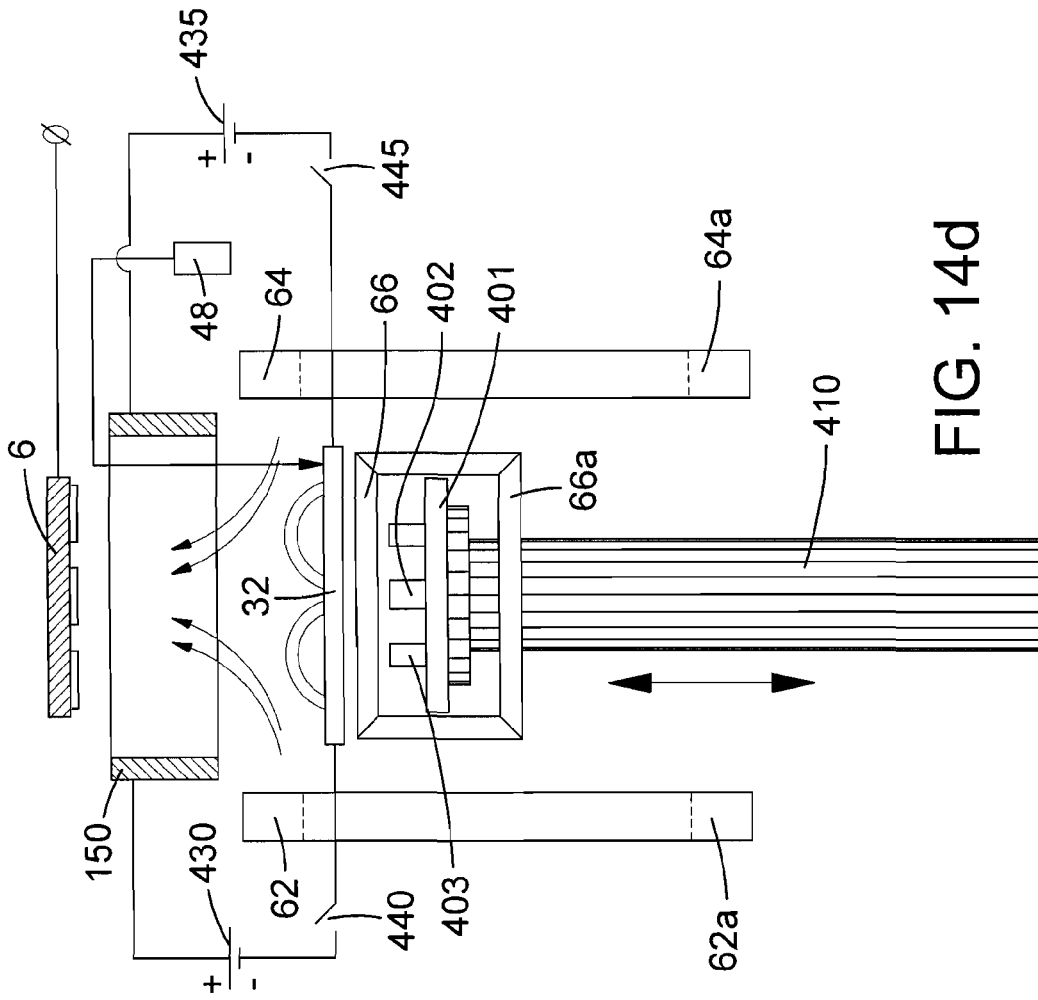


FIG. 14d

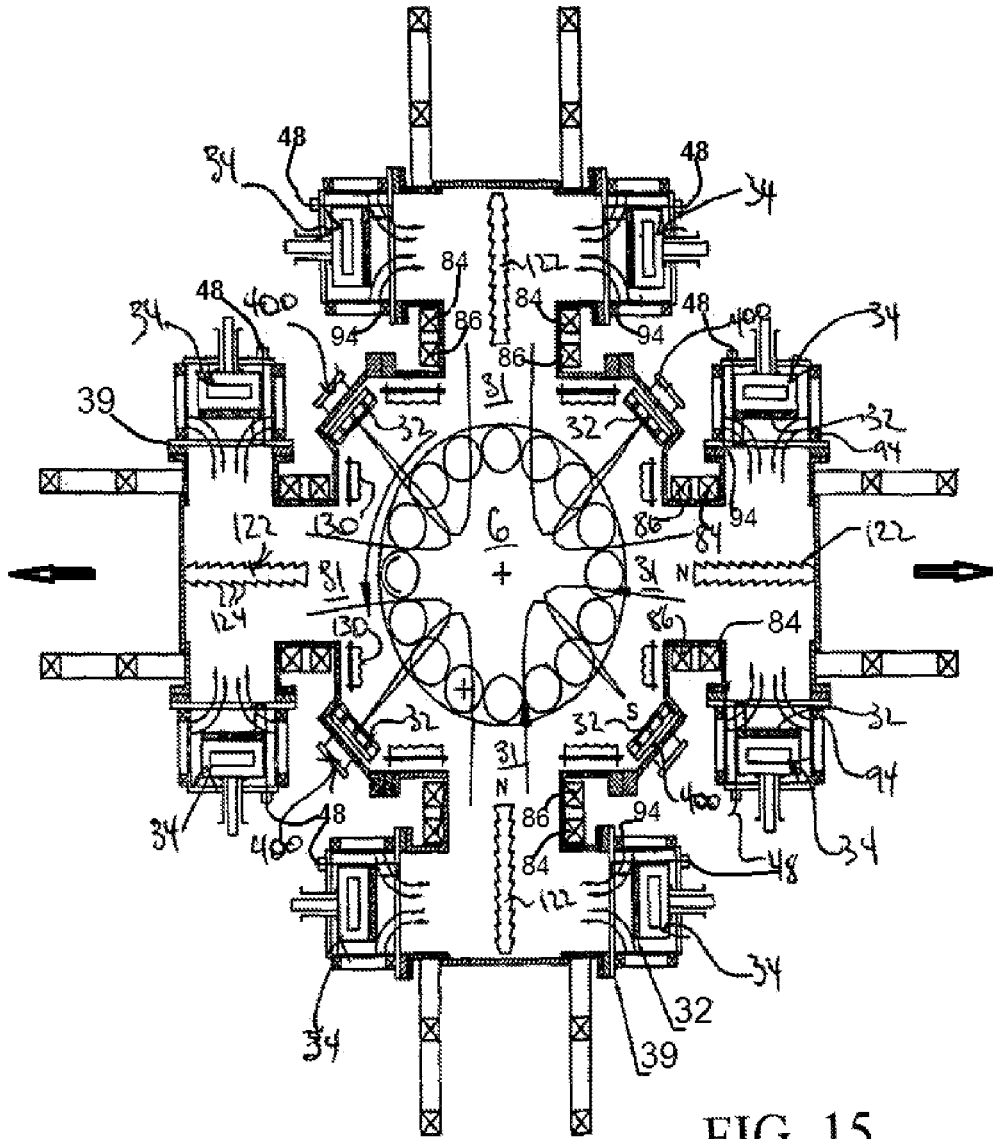


FIG. 15

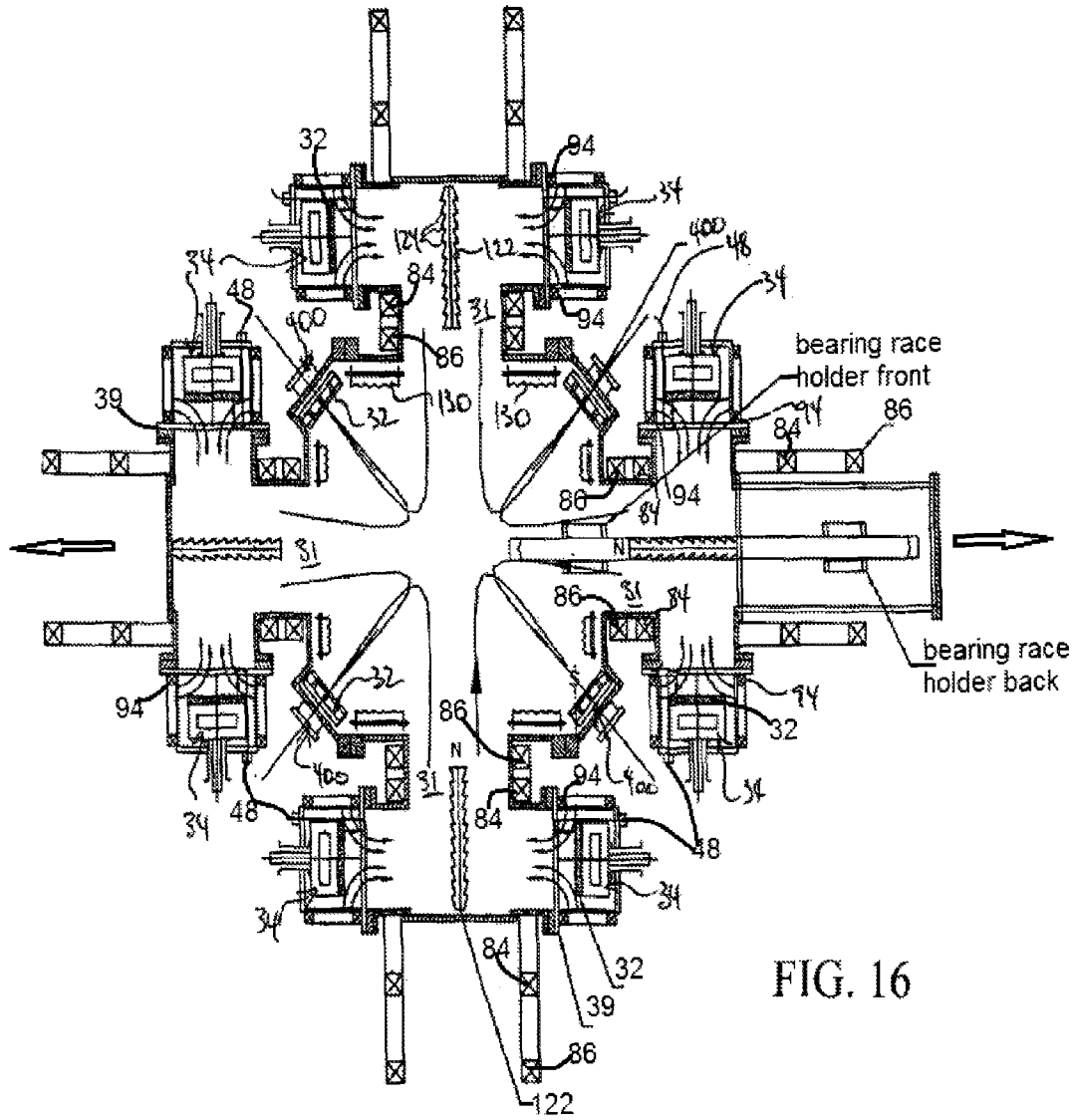


FIG. 16

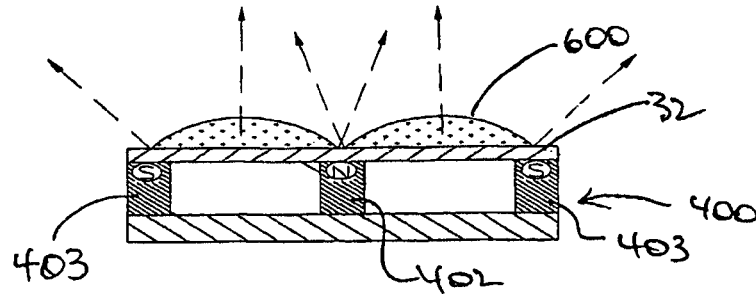


Fig. 17a

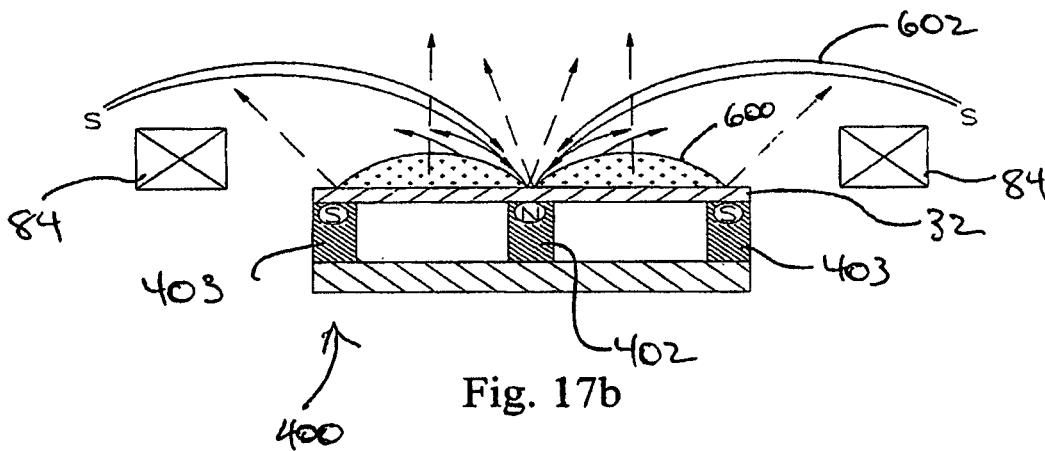


Fig. 17b

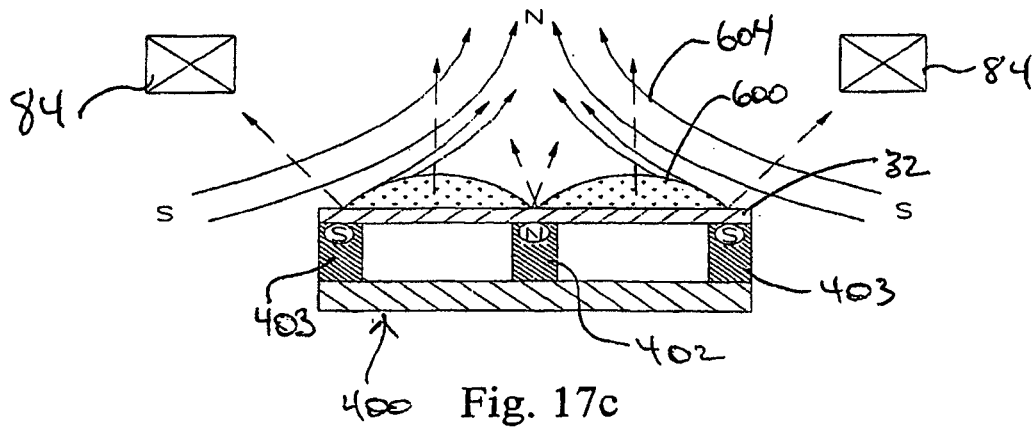


Fig. 17c

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**RECTANGULAR FILTERED VAPOR PLASMA
SOURCE AND METHOD OF CONTROLLING
VAPOR PLASMA FLOW**

CROSS-REFERENCE TO RELATED
APPLICATIONS

This application is a continuation of application Ser. No. 10/572,120, filed Mar. 16, 2006 now abandoned; which is a 371(c)(1) Application of PCT/US04/30603, filed Sep. 17, 2004, which claims the benefits of U.S. application Ser. No. 10/667,279, filed Sep. 18, 2003, now U.S. Pat. No. 6,929,727; the disclosures of which are hereby incorporated by reference in their entirety including all figures, tables and drawings.

STATEMENT REGARDING FEDERALLY
SPONSORED RESEARCH OR DEVELOPMENT

Not applicable

REFERENCE TO SEQUENCE LISTING, A
TABLE, OR A COMPUTER PROGRAM LISTING
COMPACT DISC APPENDIX

Not applicable

FIELD OF INVENTION

This invention relates to apparatus for the production of coatings in a vacuum. In particular, this invention relates to a vacuum arc coating apparatus having a rectangular filtered cathodic or magnetron arc source providing improved arc spot scanning, and a plasma focusing and filtering system.

BACKGROUND OF THE INVENTION

Many types of vacuum arc coating apparatus utilize a cathodic arc source in which an electric arc is formed between an anode and a cathode plate in a vacuum chamber. The arc generates a cathode spot on a target surface of the cathode, which evaporates the cathode material into the chamber. The cathodic evaporate disperses as a plasma within the chamber, and upon contact with one or more substrates coats the substrates with the cathode material, which may be metal, ceramic etc. An example of such an arc coating apparatus is described in U.S. Pat. No. 3,793,179 issued Feb. 19, 1974 to Sablev, which is incorporated herein by reference.

An arc coating apparatus of this type is advantageous for use in the coating of large substrates and multiple substrates, due to the large surface area of the cathode which can be evaporated into a large volume coating chamber. However, in a large surface area cathode arc coating apparatus of this type a significant portion of the target evaporation surface of the cathode plate goes largely unused, due to the scanning pattern of arc spots which follows certain physical principles:

1. The arc discharge tends to move in a direction which reduces the voltage drop in the arc circuit, and the arc spot thus tends to migrate to regions on the target surface which are closest to the anodic current conductor. Where multiple current conductors traverse the cathode the arc spot will occasionally migrate into the region between conductors where it may remain for a considerable time because no steering mechanism is present to move the arc spot back to the desired evaporation zone.

2. In the case of metal cathodes the arc spot follows a retrograde motion according to the "anti-ampere force" prin-

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ciple, and is thus attracted to the coaxial magnetic force lines generated by the anodic current conductor.

3. In the case of a cathode formed from a material which does not have a melting phase, for example a sintered or graphite cathode, the arc spot moves according to the "ampere force" principle and is repelled from the coaxial magnetic force lines generated by the anodic current conductor.

4. The arc spot is attracted to the region where the tangential component of a transverse magnetic field is strongest.

5. The arc spot tends to migrate away from the apex of an acute angle at the point of intersection between a magnetic field line and the cathode target surface (the "acute angle" rule).

These effects result in a limited erosion zone relative to the available area of the target surface of the cathode plate, reducing the life of the cathode and dispersing cathodic evaporate into the coating chamber in non-uniform concentrations.

In a large area cathode arc coating apparatus using a metal cathode plate the anti-ampere motion of the arc spot and the tendency of the arc to seek the lowest voltage drop combine to largely confine the arc spot to the vicinity of the anodic conductor, substantially limiting the erosion zone to the region of the target surface surrounding the anodic conductor.

This results in a very small area inside the coating chamber in which the cathodic evaporate is concentrated enough to apply a uniform coating to the substrates. However, it is not possible to construct the cathode plate so that the desired coating material is located only in the erosion zone, since the arc spot will occasionally stray out of the erosion zone and if the target surface is not entirely composed of the selected coating material the cathodic evaporate from outside the desired erosion zone will contaminate the coating on the substrates.

In the case of a cathode plate formed from a material which does not have a melting phase, the tendency of the arc spot to move in an ampere direction, away from the region of the anodic conductor, is opposed by the tendency of the arc discharge to settle toward the region of lowest voltage drop. In these cases the arc spot tends to move chaotically over the target surface of the cathode and the cathodic evaporate accordingly disperses in random locations and non-uniform concentrations within the coating chamber, rendering uniform coating of the substrates improbable. This random motion also causes the arc spot to move off of the target surface of the cathode and causes undesirable erosion of non-target portions of the cathode plate, for example the side edges.

U.S. Pat. No. 4,448,659 issued May 15, 1984 to Morrison, which is incorporated herein by reference, describes an arc coating apparatus providing a cathode in the form of a plate with a large target surface for creating cathodic evaporate. A confinement ring composed of a magnetically permeable material surrounds the cathode to confine the arc spot to the target surface. Such plasma sources can be used for the production of coatings on large and long articles, but present the following disadvantages:

1. Despite the initial low probability of the presence of cathodic spots on the protective ring, over time the cathodic evaporate coats the ring and cathodic spots are produced on the ring with increasing frequency. This results in contamination of the coating by the ring material, and ultimately in ring failure.

2. In self-steering cathodic arc sources it is not possible to use external magnetic fields in the vicinity of the target surface of the cathode. It is therefore not possible in such an apparatus to use a plasma-focusing magnetic field, as the influence of the focusing magnetic field makes the distribu-

tion of cathodic spots on the working surface of the cathode irregular and non-uniform. Any external magnetic field, for example for focusing or deflecting the arc plasma flow, interferes with the self-sustained magnetic field generated by the cathode and anode current conductors and disrupts the self-steering character of the cathode spot. However, the absence of magnetic focusing reduces the efficiency of the coating process and impairs the quality of substrate coatings, because the content of the neutral component (macroparticles, clusters and neutral atoms) in the region of the substrates, and thus in the substrate coating, increases.

3. A cathode in this type of plasma source rapidly becomes concave due to evaporative decomposition, and its useful life is therefore relatively short. Moreover, since the evaporation surface of the cathode becomes concave in a relatively short time it is practically impossible to use a high voltage pulse spark igniter in such a design, so that a mechanical igniter must be used which lowers working reliability and stability.

4. While the confinement ring prevents the arc spot from straying off of the target surface, it does not affect the tendency of the arc spot to migrate toward the anodic conductor in the case of metal cathodes, or to move chaotically over the target surface in the case of non-metal cathodes.

Accordingly, self-steering arc plasma sources tend to use the target surface inefficiently and the cathode thus has a relatively short useful life.

The erosion efficiency of the target surface can be improved by providing an arc spot steering system to steer the arc spot along a selected path about the target surface. This increases the size of the region within the coating chamber in which coating can occur.

For example, the scanning pattern of a cathode spot can be controlled by providing a closed-loop magnetic field source disposed beneath the target surface of the cathode, in a manner similar to that described in U.S. Pat. No. 4,724,058 issued Feb. 9, 1988 to Morrison, which is incorporated herein by reference. The magnetic field source establishes a magnetic field in a selected direction over the target surface, which directs the cathode spot in a direction substantially perpendicular to the direction of the magnetic field and thus provides more efficient evaporation of the target surface. This approach is based on the principle of arc spot motion whereby an arc spot is attracted to the region where the tangential component of a transverse magnetic field is strongest.

However, this still significantly limits the area of the target surface of the cathode which is available for erosion, because this type of arc coating apparatus creates a stagnation zone in the region where the tangential component of the magnetic field is strongest. The cathode spot eventually settles in the stagnation zone, tracing a retrograde path about the erosion zone and creating a narrow erosion corridor on the target surface. This limits the uniformity of the coating on the substrates and reduces the working life of the cathode.

U.S. Pat. No. 5,997,705 issued Dec. 7, 1999 to Welty, which is incorporated herein by reference, teaches a rectangular cathode plate in which the evaporation surface is located on the peripheral edge of the cathode plate, the arc spot being confined to the evaporation surface by cathode shields disposed over opposed faces of the cathode plate. Deflecting electrodes disposed about the cathode plate direct the plasma stream in two directions, parallel to the faces of the cathode plate.

In this apparatus the substrates must surround the edges of the cathode plate, and the cathode plate occupies most of the space within the apparatus. Thus, in order to coat a significant number of substrates the cathode plate, and thus the apparatus itself, must be extremely large. Also, filtration in this appara-

tus is poor, since the substrates are directly exposed to droplets and macroparticles entrained in the cathodic evaporate.

A deflecting electrode is described in U.S. Pat. No. 5,840,163 issued Nov. 24, 1998 to Welty, which is incorporated herein by reference. This patent teaches a rectangular vacuum arc plasma source in which a deflecting electrode is mounted inside the plasma duct and either electrically floating or biased positively with respect to the anode. However, this device requires a sensor which switches the polarity of the magnetic field when the arc spot on the rectangular source has reached the end of the cathode, in order to move the arc spot to the other side of the cathode. This results in an undesirable period where the magnetic field is zero; the arc is therefore not continuous, and is not controlled during this period. Consequently this 'pseudo-random' steering method cannot consistently produce reliable or reproducible coatings.

U.S. Pat. No. 4,673,477 to Ramalingam proposes that the magnetic field source can be moved to shift the magnetic field lines and increase the utilization efficiency of the target surface. However, the mechanical adaptations required for such a system make the apparatus too complicated and expensive to be practical.

Where an external magnetic field is present the arc spot follows the "acute angle" rule, according to which the arc spot tends to migrate away from the apex of an acute angle at the point of intersection between a magnetic field line and the cathode target surface. The basic principle is that a cathodic spot formed by a vacuum arc in a fairly strong magnetic field (in the order of 100 Gauss), the force lines of which cross the surface of the cathode at an acute angle, will move in a reverse (retrograde) direction perpendicular to the tangential component of the field and, concurrently, displace away from the apex of the angle (for example, see *Cathodic Processes of Electric Arc* by Kesaev I. G., Nauka, 1968). This results in the arc spot settling beneath the apex of the arch-shaped portion of the magnetic field which projects over the target surface.

U.S. Pat. No. 5,587,207 issued Dec. 24, 1996 to Gorokhovskiy, which is incorporated herein by reference, teaches that cathode spot confinement under a closed loop-type linear anode can be enhanced by a conductor which encases the anode to form a closed loop magnetic coil, with the magnetic field lines oriented in the direction shown in FIGS. 29 and 30 therein. Simultaneous use of both the closed-loop magnetic steering coil behind the cathode and a closed-loop linear anode in front of the target evaporation surface (with or without an enclosed magnetic coil) results in a synergistic improvement of arc discharge stability and thus cathode spot motion. The anode can be configured in any desired pattern, the configuration thereof being limited only by the periphery of the target surface. The arc spot will scan the target surface under the influence of the transverse magnetic field (in an ampere direction in the case of cathodes of carbon and related sintered materials or in an anti-ampere direction in the case of metal cathodes), virtually unaffected by the current flowing through the anodic conductor.

A disadvantage of this approach is that the arc spot will occasionally migrate from the selected erosion zone to another part of the cathode target surface where the intensity of the transverse magnetic field is small and, there being no means available to return the arc spot to the desired erosion zone, will stagnate in the low magnetic field region. In the case of a carbon-based cathode plate, when the velocity of arc spot movement is low enough the arc spot can settle in any stagnation zone where the transverse magnetic field is close to zero, and will not return to the erosion zone.

U.S. Pat. No. 5,435,900 issued Jul. 25, 1995 to Gorokhovskiy, which is incorporated herein by reference, dis-

closes a deflecting magnetic system surrounding a parallelepipedal plasma guide, in which the deflecting conductors force the plasma toward the substrate holder. However, this patent does not address the problem of magnetically steering an arc spot around a rectangular cathode plate in the presence of a deflecting magnetic field.

In case of conventional rectangular magnetron sputtering sources the magnetron plasma discharge is confined near the target surface by a closed loop magnetron magnetic field. This creates a closed loop shape of the discharge located along the magnetic corridor defined between outer and central magnetic poles where the magnetic field is strongest. In this conventional design the magnetic field is balanced between the outer and central poles. This design has the drawback of low target utilization rate and inefficient energy consumption (P. Robinson and A. Matthews, Characteristics of a Dual Purpose Cathodic Arc/Magnetron Sputtering System, Surface and Coating Technology, 43/44 (1990) 288-298, which is incorporated herein by reference). This can be also used for a dual purpose arc/magnetron vapor plasma deposition source. If the cathode target is equipped with a magnetron high voltage low current power supply and a separate low voltage high current arc power supply as well as an arc igniter, it is possible to run the target in both magnetron sputtering and arc evaporation modes. This was successfully demonstrated by running large rectangular arc/magnetron cathode targets (P. Robinson and A. Matthews, Characteristics of a Dual Purpose Cathodic Arc/Magnetron Sputtering System, Surface and Coating Technology, 43/44 (1990) 288-298). The setback of this approach is an extremely low utilization rate of the target when it is running in arc mode due to cathodic arc spots having a tendency to settle or stay in a location near the area where the tangential component of the arch-shape planar magnetron-type magnetic field is strongest.

These designs also suffer from a low ionization rate of the plasma vapor flow due to a high degree of confinement provided by the balance magnetron magnetic field. In an unbalanced magnetron magnetic system design the central pole can be weakening or removed, providing that much higher ion fluxes can be extracted from near the target magnetron discharge zone (B. Window and N. Savvides, Journal Vacuum Science and Technology A, 4 (1986) p. 196, which is incorporated herein by reference). U.S. Pat. No. 5,160,595 to Hauser, which was issued in Nov. 3, 1992, which is incorporated herein by reference, describes an arc/magnetron apparatus in which an edge magnet arrangement is displaceable in an axial direction relative to a preferably fixedly mounted center pole permanent magnet so that a cathode sputtering process and/or an arc discharge process can be realized depending on the relative position of the edge magnet arrangement and the center pole magnet. When the edge magnets are removed the central pole magnet can provide a steering magnetic field for steering arc spots in arc evaporation mode. This design allows for better utilization of cathode target material, but still suffers from a relatively small arc steering area. It also confines most of the ionized plasma flow on or near the target surface, which significantly reduces the ionization rate of vapor plasma flux and results in reduced coating adhesion.

U.S. Pat. No. 6,730,196 to Wang, which was issued in May 4, 2004, which is incorporated herein by reference, teaches that a magnetic focusing coil disposed in a processing area between the magnetron target and substrates to be coated can extract additional plasma flow from near the target area to yield higher ionization of the magnetron sputtering plasma flux. The magnetic field of this focusing coil overlaps the magnetron magnetic field, e.g. the direction of magnetic force lines of the magnetic field created by the focusing coil is

aligned with the direction of magnetic force lines created between edge poles and central poles of the magnetron magnets. One disadvantage of this design is that the focusing coil is not adapted to the shape of the magnetron target. This will result in a high non-uniformity of magnetron plasma flow when applied to rectangular magnetron targets.

Neither of the above mentioned magnetron and arc/magnetron sputtering source designs allow for the elimination of macroparticles from the magnetron plasma flow. These macroparticles are generated on the face surface of the magnetron target as a result of micro-arcing processes. This results in an increase of coating defects, which is especially detrimental for such a precision applications as metal interconnect copper, and magnetic media coatings and other semiconductor and optical coatings. It also reduces the functional properties of hard wear-resistant coatings for cutting tools, increases the coefficient of friction in coatings designated for low friction applications, and decreases the corrosion resistance of both decorative and protective coatings.

SUMMARY OF THE INVENTION

The present invention overcomes these disadvantages by providing a steering magnetic field source comprising a plurality of electrically independent closed-loop steering conductors disposed in the vicinity of the target surface. In the preferred embodiment each steering conductor can be controlled independently of the other steering conductors.

The steering conductors may be disposed in front of or behind the target surface of the cathode plate. When disposed in front of the target surface the steering magnetic field lines intersect with the target surface at an obtuse angle, which obviates the motion-limiting effect of the acute angle principle and allows the arc spot to move over a larger region of the target surface, thereby further increasing the size of the erosion zone.

Steering conductors disposed in front of the target surface can also serve as focusing conductors, which confine the plasma and direct it toward the substrates. In these embodiments opposed steering/focusing conductors disposed along the long sides of the cathode plate generate magnetic cusps which create a magnetic pathway within which the plasma flows toward the substrates. Additional focusing conductors may be disposed along the plasma duct downstream, preferably with magnetic fields that overlap within the plasma duct to create a continuous magnetic wall along the plasma duct.

Increasing the current through one steering conductor increases the strength of the magnetic field generated by that conductor relative to the strength of the magnetic field of the steering conductor along the opposite side of the cathode plate, shifting the magnetic field on the opposite side of the cathode plate transversely. Selective unbalancing of the steering conductor currents can thus compensate for the magnetic influence of the focusing conductors, and if desired can increase the effective breadth of the erosion zone to thus provide more uniform erosion of the target surface and a larger area within the coating chamber in which the cathodic evaporate is dispersed at concentrations sufficient to uniformly coat the substrates.

In a further embodiment, groups of steering conductors are disposed along opposite sides of the cathode plate. By selectively applying a current through one conductor in each group, the path of the arc spot shifts to an erosion corridor defined by the active steering conductor.

The present invention further provides means for restricting the cathode spot from migrating into selected regions of the target evaporation surface outside of the desired erosion

zone. The invention accomplishes this by providing a shield at floating potential positioned over one or more the selected regions of the target evaporation surface, which prevents the arc spot from forming in or moving into the shielded region. In one preferred embodiment the shield is positioned immediately above the region of the target surface in the vicinity of the anode, spaced from the target surface. The evaporation zone is thus restricted to the area of the target surface surrounding the shield, protecting the anode from deposition of cathodic evaporate and providing better distribution of cathodic evaporate over the substrates to be coated, which results in more uniform coatings over a greater coating area.

The shield can be used to keep arc spots away from any region where the negative conductor traverses the cathode, which represents the lowest voltage drop relative to the anode. Where a large anode or multiple anodes are provided the shield restrains the arc spot from migrating into the region of the cathode located beneath an anode, where most of evaporated material would be trapped by the anode rather than flowing to the substrate.

Further, the presence of the shield allows the target evaporation surface of the cathode plate to be constructed of a combination of the coating material and another material, for example an expensive coating material such as titanium or platinum in the desired erosion zone and an inexpensive material such as steel outside of the erosion zone. The steel portion of the target surface may be shielded by a floating shield of the invention to prevent cathode spot formation and motion thereon, and thus prevent contamination of the coating while optimizing utilization of the expensive coating material.

In an arc coating apparatus utilizing a magnetic steering system, regions where the transverse magnetic field is low can be shielded in the same manner to exclude movement of the arc spot into these regions and create the desired pattern of erosion. In this embodiment of the invention the target may be placed on the poles of magnetron-type magnetic system of the type described in U.S. Pat. No. 4,724,058 issued Feb. 9, 1988 to Morrison, which is incorporated herein by reference. The region of the evaporation surface located about the central part of target cathode, where the tangential component of the magnetic field is too weak to confine arc spots, may be shielded by a floating shield which prevents the arc spot from migrating into the stagnation area created between the magnetic fields generated by the magnetron.

The invention further provides a magnetic focusing system which confines the flow of plasma between magnetic fields generated on opposite sides of the coating chamber. This prevents the plasma from contacting the surface of the housing, to avoid premature deposition, and increases the concentration of plasma in the vicinity of the substrate holder.

In a further embodiment the plasma focusing system can be used to deflect the plasma flow off of the working axis of the cathode, to remove the neutral component of the plasma which otherwise constitutes a contaminant. In this embodiment the plasma focusing coils are disposed in progressively asymmetric relation to the working axis of the cathode, to deflect the flow of plasma along a curvate path toward a substrate holder.

The present invention thus provides a vacuum arc coating apparatus comprising at least one rectangular cathode plate having opposed long sides connected to a negative pole of a current source, the at least one cathode plate having a target surface comprising an evaporation surface or a sputtering surface, or both, a coating chamber in communication with the target surface, a substrate holder within the coating chamber, at least one anode within the coating chamber spaced

from the target surface, connected to a positive pole of a current source, and a magnetic deflecting system comprising at least first and second conductors arranged along opposite long sides of the at least one cathode plate, the first conductor carrying a current in a direction opposite to a direction of current in the second conductor, the first and second conductors each being disposed in front of and in the vicinity of the target surface so that a magnetic field generated thereby focuses a flow of vapour plasma from the target surface toward the substrate holder, the first conductor being electrically independent of the second steering conductor, wherein by varying a level of current applied through the first conductor relative to the second conductor the flow of vapor plasma shifts toward the coating chamber.

The present invention further provides a vacuum arc coating apparatus comprising at least one magnetron arc source comprising at least one rectangular cathode plate having opposed long sides, connected to a negative pole of a current source, and sets of magnets disposed behind the at least one cathode plate, the at least one cathode plate having a target surface comprising an evaporation surface or a sputtering surface, or both, an anode, a coating chamber in communication with the target surface and a housing, a substrate holder within the coating chamber, a plasma guide disposed between the at least one cathode plate and the coating chamber, the cathode plate being out of optical alignment with the substrate holder, and a set of first focusing conductors disposed in front of and generally parallel to the long sides of the at least one cathode plate, for creating a half-cusp configuration of focusing magnetic field lines converging in front of the target surface along the long sides to extract plasma from the arch-shaped magnetron magnetic fields and direct the plasma toward the coating chamber.

The present invention further provides vacuum arc coating apparatus comprising at least one magnetron arc source comprising at least one rectangular cathode plate having opposed long sides, connected to a negative pole of a current source, and sets of magnets disposed behind the at least one cathode plate, the at least one cathode plate having a target surface comprising an evaporation surface or a sputtering surface, or both, an anode, a coating chamber in communication with the target surface, a substrate holder within the coating chamber, a plasma guide disposed between the at least one cathode plate and the coating chamber, the at least one cathode plate being disposed in the plasma guide, a north pole of the magnetron magnetic field being located at the exit of the filtered arc source and a south pole of the magnetron magnetic field being located generally centrally relative to the magnetron, or a south pole of the magnetron magnetic field being located at the exit of the filtered arc source and a north pole of the magnetron magnetic field being located generally centrally relative to the magnetron, whereby magnetic field lines exiting from the filtered arc source reach the evaporation surface, at least one filtered cathodic arc source out of optical alignment with the substrate holder and adjacent to the at least one magnetron arc source, and a set of conductors disposed in front of and generally parallel to the long sides of the target surface, for creating focusing magnetic field lines to magnetically couple the magnetron arc source to the filtered arc source and thereby extract plasma from the magnetron and the filtered cathodic arc source and direct the plasma toward the coating chamber.

The present invention further provides a method of controlling a flow of plasma in a vacuum arc coating apparatus comprising at least one magnetron arc source comprising at least one rectangular cathode plate having opposed long sides and connected to a negative pole of a current source and

having a target surface comprising an evaporation surface or a sputtering surface, or both, an anode, and a coating chamber in communication with the target surface containing a substrate holder comprising the steps of: a. generating at least one cathode spot on the target surface to create a plasma, and b. generating a deflecting magnetic field having deflecting magnetic field lines overlapping with magnetron magnetic field lines generated by the magnetron, the deflecting magnetic field lines and the magnetron magnetic field lines having the same transverse direction, whereby the deflecting magnetic field draws plasma from the magnetron magnetic field and deflects the plasma toward the coating chamber.

In a further aspect of the method of the invention, a current through the deflecting conductors on opposite sides of the target surface can be controlled independently.

Further aspects and embodiments of the invention and of apparatus for implementing the methods of the invention will be apparent from the detailed description which follows.

BRIEF DESCRIPTION OF THE SEVERAL VIEWS OF THE DRAWING

In drawings which illustrate by way of example only a preferred embodiment of the invention,

FIG. 1 is a schematic cross-section of a prior art large area cathode vacuum arc plasma source having a magnetic steering system disposed behind the cathode plate;

FIG. 2 is a partial perspective view illustrating the distribution of magnetic field lines produced by a magnetic steering system according to one embodiment of the invention;

FIG. 2a is a schematic elevation illustrating balanced magnetic field lines produced by the magnetic steering system of FIG. 2;

FIG. 2b is a schematic elevation illustrating an erosion corridor produced by the magnetic steering system of FIG. 2 unbalanced in a first direction;

FIG. 2c is a schematic elevation illustrating an erosion corridor produced by the magnetic steering system of FIG. 2 unbalanced in a second direction;

FIG. 3 is a schematic elevation illustrating a variation of the embodiment of FIG. 2 in which multiple steering conductors are disposed along the long sides of the cathode plate;

FIG. 4 is a plan view of a further preferred embodiment of a large area cathode arc source of the invention;

FIG. 5 is a cross-section of the apparatus of FIG. 4 taken along the line 5-5;

FIG. 6a is a cross-section of the apparatus of FIG. 4 taken along the line 6-6;

FIG. 6b is a cross-sectional elevation of a further embodiment of the apparatus of FIG. 4 having multiple pairs of steering conductors;

FIG. 7a is a plan view of an arc coating apparatus embodying a plasma focusing system according to the invention having a plurality of linear anodes and a single cathode target;

FIG. 7b is a side elevation of the arc coating apparatus of FIG. 7a;

FIG. 7c is a side elevation of the arc coating apparatus of FIG. 7a with plurality of cathode targets installed in the same housing; FIG. 7d is a plan view of an arc coating apparatus of FIG. 7c;

FIG. 8 is a plan view of a variation of the arc coating apparatus of FIG. 7a providing neutralizing conductors for modulating the steering and focusing conductors;

FIG. 9 is a plan view of an arc coating apparatus embodying a deflecting electromagnetic system according to the invention for guiding cathodic evaporate to a substrate holder disposed remote from the working axis of the cathode plate;

FIG. 10a is a plan view of a dual arc coating apparatus embodying the magnetic steering, focusing and deflecting aspects of the invention;

FIG. 10b is a plan view of a dual arc-magnetron coating apparatus embodying the magnetic steering, focusing and deflecting aspects of the invention;

FIG. 10e is a plan view of a dual magnetron coating apparatus embodying the magnetic steering, focusing, deflecting and auxiliary arc ionizing aspects of the invention;

FIG. 11 is a cross-sectional side elevation of a further embodiment of the arc coating apparatus according to the invention;

FIG. 12 is a cutaway front elevation of the arc coating apparatus of FIG. 11;

FIG. 13 is a rear elevation of the arc coating apparatus of FIG. 11;

FIG. 14a is a partial perspective view of the arc-magnetron coating apparatus embodying the magnetic steering, focusing and deflecting aspects of the invention;

FIG. 14b is a cutaway front elevation of the arc-magnetron coating apparatus of FIG. 14a;

FIG. 14c is a cross-sectional side elevation of the arc-magnetron coating apparatus of FIG. 14a taken along a longitudinal centre of the magnetron target;

FIG. 14d is a cross-sectional side elevation of the arc-magnetron coating apparatus of FIG. 14a taken along a transverse centre of the magnetron target;

FIG. 15 is a schematic plan view of an embodiment of the invention having four magnetrons coupled in a dual filtered-arc source configuration;

FIG. 16 is a schematic cross-sectional plan view of a processing chamber having multiple pairs of opposed rectangular filtered arc-magnetron coating stations with loading of the large bearing race in a vertical rotational alignment; and

FIGS. 17a to 17c are schematic elevational views of a magnetron showing the influence of magnetic field lines generated by the magnetron and deflecting conductors.

DETAILED DESCRIPTION OF THE INVENTION

FIG. 1 illustrates a prior art large area rectangular cathode vacuum arc plasma source of the type described and illustrated in U.S. Pat. No. 4,724,058 to Morrison, which is incorporated herein by reference. The apparatus 10 comprises a cathode plate 12 having a target surface comprising evaporation surface 14 which may be circumscribed by a confinement member 16 composed of a magnetically permeable material. As described in U.S. Pat. No. 5,587,207 issued Dec. 24, 1996 to Gorokhovskiy, which is incorporated herein by reference, an anode 15 disposed opposite the target surface 14, which may be composed of a metallic or a non-metallic coating material.

A current applied between the cathode 12 and the anode 15 creates an arc which generates an arc spot on the target surface 14. In the prior art apparatus shown the scanning pattern of the cathode spot is controlled by a closed-loop magnetic field source 18 disposed behind the cathode 12. The magnetic field source 18 establishes magnetic fields 19a, 19b in a opposite directions over the target surface 14 which moves the arc spot in a retrograde motion according to the formula

$$V_{cs} = -cI_{cs}(B_t)$$

in which V_{cs} is the velocity of the arc spot, I_{cs} is the arc spot current, B_t is the strength of the transverse magnetic field, and c is a coefficient based on the material of the target surface 14. The arc spot thus traces a retrograde path about the cathode plate following the length of the magnetic field source.

When trapped within the static magnetic field produced by the magnetic field source **18**, the cathode spot is directed toward the apex of the magnetic field lines **20**, the region where the tangential component of a magnetic field is strongest, which causes the target surface **14** to evaporate along a narrow evaporation corridor **14a**. Further, the oppositely oriented magnetic field lines **19a**, **19b** create a stagnation zone at **22** in which the cathode spot can settle and remain for prolonged periods, eroding the target surface **14** unduly in the stagnation zone **22**. Both of these effects result in poor utilization efficiency of the target surface **14**. Accordingly, in the apparatus described in U.S. Pat. No. 4,724,058 the magnetic field is activated only intermittently during the coating process, the arc spot being free to scan randomly most of the time. Since the cathode spot is largely self-steering, magnetic fields cannot be used for plasma focusing.

FIG. 2 illustrates a preferred embodiment of a cathode spot steering system **60** according to the invention. In the embodiment illustrated in FIG. 2 the steering system **60** is disposed behind the cathode plate **32** (i.e. on the side of the cathode plate **32** opposite to the target evaporation surface **34**), which has long sides **32a**, **32b** and short sides **32c**, **32d**. The steering system **60** comprises linear conductors **62** and **64** respectively disposed in parallel with the long sides **32a**, **32b** of the cathode plate **32** having a current I_{LS} applied thereto in the direction shown, and linear conductors **66** and **68** respectively disposed in parallel with the short sides **32c**, **32d** of the cathode plate **32** having a current I_{SS} applied thereto in the direction shown. The conductors **62**, **64** are disposed behind the cathode plate in the vicinity of the target surface **34** so that the magnetic fields generated thereby intersect the target surface **34**, and thus influence arc spot formation and motion. The steering conductors **62**, **64**, **66**, **68** may alternatively be disposed in front of the cathode plate, as in the embodiment illustrated in FIGS. 4 to 6, described below. In either case the steering magnetic field source **60** generates a magnetic field defining an erosion zone **70** along the target surface **34**.

The configuration and polarities of the magnetic fields generated by the steering conductors **62**, **64**, **66** and **68** are illustrated by the magnetic field lines in FIG. 2. The magnetic field lines projecting above the target surface **34** are arch-shaped, and on opposite sides of the cathode **32** are oriented in opposite directions. Arc spots moving within the erosion zone **70** are attracted toward the apex of the arch-shaped magnetic field lines, where the tangential component of the magnetic field which projects beyond the target surface **34** is strongest. When the current through opposite conductors, for example steering conductors **62** and **64**, is equal or balanced (i.e. $I_1=I_2$), the arc spot travels along a narrow erosion corridor largely confining the erosion zone **70** beneath the apex of the magnetic field lines symmetrically about the longitudinal centre of the cathode plate **32**, as shown in FIG. 2a.

According to one aspect of the invention, by increasing the current in one steering conductor relative to the current in the steering conductor on the opposite side of the cathode plate **32**, the magnetic field becomes unbalanced and the magnetic field lines on the side of the cathode **32** with the weaker magnetic field shift toward the side of the cathode **32** with the stronger magnetic field. In the preferred embodiment each linear conductor **62**, **64**, **66**, **68** is thus electrically independent and can be controlled in isolation.

For example, in FIG. 2b the current in steering conductor **62** has been increased relative to the current in steering conductor **64**, so that $I_1 < I_2$. The resulting unbalancing of the strength of the magnetic fields generated thereby distorts the magnetic field generated by the conductor **64** and shifts its magnetic field lines toward the conductor **62**. The point of the

magnetic field generated by conductor **64** where the tangential component of the transverse magnetic field is strongest has thus shifted away from the side **32a** and toward the centre of the cathode **32**, and arc spots accordingly trace a path closer to the centre of the cathode **32**. By unbalancing the current in conductors **62**, **64** so that conductor **64** generates the stronger magnetic field and $I_1 > I_2$, the path of the arc spot shifts away from the side **32b** and toward the centre of the cathode, as shown in FIG. 2c.

The degree of unbalancing, i.e. the current differential between conductors **62** and **64**, determines the extent of the magnetic field shift. By unbalancing the conductors **62**, **64** at selected current levels and in properly timed intervals coinciding with the motion of the arc spot, a plurality of arc spot paths are created. This substantially increases utilization efficiency of the target surface.

A similar effect is achieved along the short sides **32c**, **32d** of the cathode **32** by unbalancing the current through the conductors **66**, **68**. The path of the arc spot will shift toward the centre of the cathode **32** along the side with the weaker magnetic field. However, it will be appreciated that if the cathode plate **32** is narrow enough that the magnetic fields generated along the long sides **32a**, **32b** by conductors **62**, **64** are relatively close together, the conductors **66**, **68** along the short sides **32c**, **32d** may become unnecessary; the arc spot will naturally migrate back and forth between the long magnetic fields, or as the arc spot reaches the end of its path along one long side **32a** or **32b** the magnetic field can be selectively decreased or momentarily deactivated along that side and the arc spot will move to the other side **32b** or **32a** where the magnetic field is stronger.

The closing conductors **62a**, **64a**, **66a**, **68a**, which are parallel to the target surface **34** and respectively complete the circuit for each steering conductor **62**, **64**, **66**, **68**, are maintained well away from the cathode plate **32** and the housing **38**. This ensures that the magnetic fields generated by the closing conductors **62b**, **64b**, **66b**, **68b** or **72a**, **72b** do not influence arc spot formation or plasma flow patterns.

In operation, when an arc is created by applying a current between the anode and the cathode plate, an arc spot generated on the target surface **34** settles in an erosion corridor **70** defined within the steering magnetic fields generated by the steering conductors **62**, **64**, **66**, **68**. The arc spot follows a retrograde motion along the erosion zone **70**. The magnetic field is periodically unbalanced by a control switch (not shown), which intermittently increases the current through conductor **62** to increase the strength of the magnetic field generated thereby and shift the arc spot path away from the side **32a**, and alternately increases the current through conductor **64** to increase the strength of the magnetic field generated thereby and shift the arc spot path away from the side **34a**. This effectively widens the erosion zone **70** to increase the utilization efficiency of the target surface, improving the quality of the coating and the durability of the cathode **32**.

In a variation of this embodiment, illustrated in FIG. 3, a plurality of steering conductors **62b**, **62c**, **62d** and **64b**, **64c**, **64d** are provided respectively along the long sides of the cathode plate **32**. In this variation the steering conductors **62b**, **62c**, **62d** and **64b**, **64c**, **64d** are activated or modulated alternately so that the erosion corridor, being located generally above the currently active steering conductor **62b**, **62c** or **62d** on one side and **64b**, **64c** or **64d** on the other side, can be shifted in a widthwise direction over the cathode plate **32** to increase the breadth of the erosion zone **70**.

In the embodiment of FIG. 3 as many steering conductors may be provided as the size of the cathode plate **32** will practically allow. One steering conductor **62b**, **62c** or **62d** and

64b, 64c or 64d should be active on each side of the cathode plate 32 at any particular time, in order to avoid creating a stagnation zone in which the cathode spot may become trapped. However, where the conductors on each side of the cathode 32 are close together, simultaneously exciting more than one conductor on each side of the cathode 32 can allow for a more elaborate erosion pattern which, properly controlled, can increase the utilization efficiency of the target surface 34 even further.

In the operation of this embodiment, when an arc is created by applying a current between the anode and the cathode plate, an arc spot generated on the target surface 34 settles in an erosion corridor 70 defined within the steering magnetic fields generated by the active steering conductors, for example 62b and 64b. The magnetic field is periodically shifted by a control switch (not shown), which switches the current between the conductors 62b, 62c and 62d on the long side 32a and between the conductors 64b, 64c and 64d on the long side 32b, to thereby and shift the arc spot path to the vicinity of the active steering conductor. This widens the erosion zone 70 to increase the utilization efficiency of the target surface, improving the quality of the coating and the durability of the cathode 32.

It will be appreciated that in each of these embodiments the active steering conductor does not need to be deactivated completely when another steering conductor is activated, or fully energized when activated, in order to achieve the desired erosion pattern in the erosion zone 70. The current can be modulated differentially as between the various steering conductors to generate the same result.

FIGS. 4 to 6 illustrate a further embodiment of the invention providing arc spot shielding. An arc coating apparatus 30 is provided with a rectangular cathode plate 32 comprising a target evaporation surface 34 and a supporting plate 36 mounted to a cathode holder 42, within a coating chamber defined by the target surface 34 and a housing 38. In the preferred embodiment the target surface 34, which may be composed of any suitable metallic or a non-metallic coating material, has long sides 32a, 32b and short sides 32c, 32d and is electrically insulated from the housing 38 by dielectric spacers 39 isolating the cathode holder 42 from the supporting plate 36 and spaced from the housing 38 by a gap 40. The target surface 34 may be formed from different materials, for example titanium and aluminum or titanium and chromium, integrated in a mosaic fashion along the erosion zone 70 to produce a composite metallic plasma for applying coatings such as TiAlN, TiCrN or the like.

The cathode plate 32 is spaced from the cathode holder 42 to create a coolant chamber 44 for circulating a coolant such as water, and is connected to the negative pole of an arc current source (not shown). A conventional high voltage pulse igniter 48 is mounted through a dielectric sleeve traversing the wall of the housing 38.

Suspended from the housing 38 by a mounting assembly 51 is a plurality of linear anodes 50, spaced from the cathode plate 32 and mounted to respective anode holders 52 which may be provided with a coolant channel 53 for circulation of a coolant such as water. The anodes 50 are connected to the positive pole of the arc current sources 46. In the preferred embodiment the anodes 50 each comprise a series of baffles or "fins" 50a which may be disposed generally orthogonally in relation to an anode body 50b, to increase the effective anodic surface area. The fins 50a and anode body 50b are each preferably oriented in a direction parallel to the direction of the plasma flow, i.e. parallel to the direction of any focusing magnetic fields in the vicinity of the anode 50 as described

below, to reduce the opportunity for vapour deposition on the anodic surfaces and thus reduce diffusion losses.

Arc spot formation is confined by steering magnetic fields produced by a steering magnetic field source 60 comprising linear conductors 62 and 64 respectively disposed along the long sides 32a, 32b of the cathode plate 32 and linear conductors 66 and 68 respectively disposed along the short sides 32c, 32d of the cathode plate 32. In this embodiment the conductors 66, 68 are disposed behind the cathode plate 32 as in the previous embodiments, but the conductors 62, 64 are disposed in front of the cathode plate 32. The conductors 62, 64 are still disposed in the vicinity of the target surface 34 so that the magnetic fields generated thereby influence arc spot formation and motion, and the operation of the steering system 60 in this embodiment is substantially as described in respect of the embodiment of FIG. 2.

However, in the embodiment of FIGS. 4 to 6 the steering magnetic fields do not confine arc spots, as in the embodiment of FIG. 2, because the magnetic field lines are not arch-shaped and intersect the target surface 34 on only one side, as seen by the magnetic field lines shown in FIG. 5. Thus, because of the acute angle principle arc spots are guided toward the central region of the cathode plate 32, away from the acute angle formed where the magnetic field lines intersect the target surface 34. Arc spots therefore have a broader range of motion available in this embodiment. Moreover, in the embodiments in which the steering conductors are located behind the cathode plate 32, in which the portion of the steering magnetic fields projecting above the target surface 34 is closed (i.e. intersects the target surface 34 along both sides), the magnetic fields confine not only the arc spot but also the plasma generated as the target surface 34 evaporates. As shown in FIG. 5, by disposing the conductors 62, 64 in front of the target surface 34 the cathodic evaporate has an open path to the substrate holder 6.

Arc spots are thus guided toward the central region of the cathode plate 32, from both long sides 32a, 32b. To avoid creating a stagnation zone in the central region of the cathode plate 32, a conductive shield 54 maintained at floating potential is mounted to each anode holder 52, insulated therefrom and spaced from the target evaporation surface 34, which precludes any cathode spot activity in the central region of the cathode plate 32. Preferably the shield 54 is spaced from the target surface 34 between 2 mm and 6 mm; less than about 2 mm is likely to cause the arc to short circuit through the shield 54 and more than about 6 mm allows the arc spot to creep under the edges of the shield 54. The shield 54 thus prevents evaporation of the cathode 32 in the shadow of the anode 50, confining arc spot formation to an erosion zone 70 surrounding the shadow of the anode 50. This protects the anode 50 from deposition of cathodic evaporate and provides a better distribution of coating material over the substrates (not shown) mounted on the substrate holder 6.

One or more floating shields 54 may be positioned over any selected portion(s) of the target evaporation surface 34, to prevent arc spots from moving into the shielded region. In the embodiment illustrated the shield 54, positioned immediately above the target surface 34 in the vicinity of the anode 50, prevents arc spots from forming in or moving into the area of the target surface 34 surrounding the shield 54. This is advantageous in embodiments in which the steering conductors are disposed in front of the cathode plate 32. However, a floating shield 54 can be used to keep arc spots away from any desired region of the cathode plate 32. For example, the floating shield 54 allows the target evaporation surface of the cathode plate to be constructed of more than one material; in this case an expensive coating material such as tungsten or platinum

can be omitted from the region beneath the shield 54, and since arc spots will not form or move in that region there is no possibility that the coating will be contaminated.

In operation, a current is applied between the anode 50 and the cathode plate 32 and a high pulse voltage applied to igniter 48 initiates a vacuum arc on the target evaporation surface 34 of the cathode plate 32. The arc spot settles in an erosion corridor 70 defined between the steering magnetic fields generated by the conductors 62, 64 and the shielded region of the target surface 34 behind the conductive shields 54. The arc spot follows a retrograde motion along one long side 32a or 32b of the target surface 34, and moves to the other long side 32b or 32a traveling beneath the apex of the magnetic field generated by the steering conductor 66 or 68 disposed behind the cathode plate 32. As the target surface 34 evaporates the plasma is guided between the magnetic fields generated by the conductors 62, 64 and flows toward the substrate holder 6, as shown by the arrows in FIG. 5.

Because the preferred embodiments of the invention employ a magnetic steering system, it is possible to use a plasma focusing system to guide the cathodic evaporate toward the substrate holder 6. A magnetic field forms a barrier which is largely opaque to plasma. Thus, focusing magnetic fields can be generated about the housing 38 to confine the plasma to a plasma flow region between magnetic fields, and positioning the substrate holder 6 in the plasma flow region to increase the concentration of plasma about the substrates and improves the quality of the coating.

In the embodiment illustrated in FIGS. 4 to 6 the conductors 62, 64, being disposed in front of the target surface 34 of the cathode plate 32, can also serve as focusing conductors in a plasma focusing system 80. A plasma flow path is defined between the magnetic fields generated by the conductors 62, 64, as shown by the magnetic field lines in FIG. 5, such that plasma is guided along a central region of the housing 38 to the substrate holder 6. In this embodiment it is advantageous to provide the short side steering conductors 66, 68 with separate power sources, which allows for the strength of their respective magnetic fields to be varied independently, to compensate for any distortion in the steering magnetic fields caused by the long side steering conductors 62, 64 and thus properly position the arc spot in the erosion corridor 70.

In the embodiment illustrated in FIG. 6b, a plurality of pairs of steering conductors 66, 68 are provided behind a single cathode plate 32, corresponding to the plurality of anodes 50. In this embodiment a separate erosion corridor can be provided for each anode 50, respectively associated with each pair of steering conductors 66, 68 parallel to the short sides of the cathode plate 32, because the two intermediate steering conductors 66, 68 prevent arc spots from migrating past the center of the cathode plate 32.

To focus the plasma flow, additional plasma focusing conductors may be provided in series to elongate the plasma flow path. For example, FIGS. 7a to 7d illustrate embodiments of the invention having a plurality of linear anodes 50 in which groups of plasma focusing conductors 82, 84 and 92, 94 are disposed on opposite sides of the housing 38 and, within each group, progressively further from the cathode 32. This creates a plasma confining zone between the magnetic fields generated on opposite sides of the housing 38, thus defining a plasma flow path between the target surface 34 and the substrate holder 6.

The focusing conductors 82, 84 and 92, 94 are preferably disposed too far from the cathode plate 32 to influence arc spot formation or motion. Preferably also the focusing conductors in each group 82, 84 or 92, 94 are disposed in closely spaced relation so that their respective magnetic fields over-

lap to create a continuous magnetic path confining the plasma flow and magnetically isolating the wall of the housing 38 from the plasma flow; otherwise plasma may be trapped against the walls of the housing 38. As in the case of the steering conductors, the closing conductors 82a, 84a of the focusing conductors 82, 84 and the closing conductors 92a, 94a of the focusing conductors 92, 94 are maintained well away from the housing 38 and the cathode plate 32 to eliminate any canceling effect of the magnetic fields generated thereby in the region of the housing 38 (plasma duct). In this embodiment it may be advantageous to provide the short side steering conductors 66, 68 with separate power sources, to compensate for any distortion in the steering magnetic fields caused by the focusing conductors 92, 94.

In the operation of this embodiment, as the target surface 34 evaporates the plasma is concentrated between the focusing magnetic fields generated by focusing conductors 82, 84 and 92, 94. The plasma thereby flows toward the substrate holder 6 without contacting the housing 38.

The focusing conductors 82, 84 and 92, 94 are preferably independently powered, so that the intensity of the magnetic field generated by each conductor 82, 84, 92, 94 can be varied independently of the others. Closed loop focusing conductors can be disposed around the housing 38, however in the preferred embodiments illustrated in FIGS. 7a, 7b pairs of independent focusing conductors 82 and 92, and 84 and 94, respectively, are disposed on opposite sides of the housing 38 parallel to the long sides 32a, 32b of the cathode 32. The closing conductors 82a, 84a, 92a and 94a are maintained well away from the housing 38 and the cathode plate 32.

In a further embodiment illustrated in FIG. 8 the opposed focusing conductors 82, 92 and 84, 94 are formed from the same closed loop conductor with the focusing conductors 82, 92, 84 and 94 disposed parallel to the long sides 32a, 32b of the cathode 32 with closing conductors 82a, 92a, 84a and 94a disposed parallel to the short sides 32c, 32d of the cathode 32.

By connecting focusing conductors 82, 84 and 92, 94 independently to the power supply it is also possible to "raster" the plasma flow by varying the current through opposed focusing conductors 82, 92 and/or 84, 94. This helps to distribute the plasma more uniformly about the plasma duct and to create a more homogeneous plasma mixture. Within the coating chamber the focusing conductors 82, 84 and 92, 94 can be independently activated to deflect pass toward the substrate holder 6.

FIG. 8 illustrates a mode of reducing the magnetic influence of the closing conductors 82a, 92a using neutralizing conductors 140 comprising closed-loop coils disposed alongside closing conductors 82a, 92a, but in an opposite orientation. When activated the neutralizing conductors 140 eliminate the influence of closing conductors 82a, 92a on the plasma flow. The neutralizing conductors 140 can also raster the plasma flow slightly in the vicinity of the walls of housing 38 parallel to the short sides 32c, 32d of the target 32.

In all embodiments the closing conductors 82a, 84a, 92a and 94a are maintained well away from the housing 38 and the cathode plate 32 to eliminate any canceling effect of the magnetic fields generated thereby in the region of the housing 38 (especially the plasma duct region of the housing 38).

The plasma focusing system of the invention can be also used to control vapor plasma flow generated by rectangular magnetron sputtering source, shown in FIGS. 14a to 14d, in which the target surface is a sputtering surface 34. In this embodiment, the focusing conductors 62, 64, which are parallel to long side of the target plate 32, are disposed in front of the target plate 32, while the closing conductors 62a, 64a are disposed beside the target plate 32 as shown in FIG. 14a. This

creates a half-cusp configuration of the focusing magnetic field lines, converging in front of the target plate 32. The closed loop magnetron discharge is created in the vicinity of the operating surface of the target plate 32 when the power supply 430 is turned on by switch 440. The discharge current is conducted between target plate 32 serving as cathode and surrounding anode 150, as shown schematically in FIGS. 14c and 14d. The vacuum chamber itself can optionally serve as an anode. The magnetron magnetic field is created in the vicinity of the target surface 34 of the target plate 32 by sets of edge magnets 403, central magnets 402 and end magnets 407. All magnets are preferably installed to a movable magnet holding plate 401.

In the operation of the embodiment of FIGS. 14a to 14d, argon as a sputtering gas is injected through the gas inlets (not shown) into the vacuum chamber, preferably in the vicinity of magnetron target 32. The high voltage, low current power supply 430 is activated to supply high negative voltage to the magnetron target 32. The magnetron plasma discharge is ignited at a pressure ranging from 0.5 mtorr to 0.5 torr. The magnetron plasma discharge will be largely confined by the arch-shaped magnetron magnetic field in the vicinity of the magnetron target cathode plate 32, forming a nearly rectangular plasma ring along the gap formed between the edge magnet set 403, the central magnet set 402 and the end magnets 407, best seen in FIG. 14b. The erosion zone will be formed by plasma sputtering on the surface of the magnetron target 32 along the path of the magnetron closed-loop discharge, where the plasma density is strongest. The focusing magnetic field created by focusing conductors 62 and 64 will create converging half cusp magnetic field lines in front of the magnetron target 32, which will extract vapor plasma from the magnetron discharge and focus it toward the substrates to be coated on substrate holder 6.

The magnetron sputtering source can be optionally equipped with a high current low voltage arc power supply 435 and arc igniter 48 which allow the source to be used in a cathodic arc evaporation mode. To increase the target utilization rate, the magnetron magnet plate 401 can be attached to a movable shaft 410, which allows the magnets to be moved away from the cathode target 32. In this case the current conductors 64, 62 arranged along the long sides of the target 32 and, independently, current conductors 66, 68 arranged along the short sides of the target 32, are used for steering arc spots along an erosion corridor on the evaporation surface of the cathode target 32.

The plasma focusing system of the invention can also be used as a plasma deflecting system 100, allowing the substrate holder 6 to be disposed remote from the working axis of the cathode plate 32, designated 33 in FIG. 9, to eliminate from the plasma the neutral component (macroparticles, clusters and neutral atoms) which are unaffected by the focusing magnetic field and further improve the quality of the coating. As shown in FIG. 9, by arranging deflecting conductors 86, 87, 88 and 96, 97, 98 along a curvate housing 38 in a progressively asymmetrical pattern relative to the working axis 33 of the cathode plate 32, the plasma is deflected toward the substrate holder 6 while the inertia of the plasma causes the neutral component to separate from the plasma in the deflection region.

In FIG. 9 the primary vapor plasma source can be cathodic arc source (as shown in FIG. 9) or a magnetron source. This FIG. 9 thus illustrates how the deflecting conductors 86, 96, 87, 97, and 88, 98 can deflect the vapor plasma flow.

The conductors 86, 87, 88 and 96, 97, 98 thereby create a chain of deflecting conductors to form a deflecting electromagnetic system. As in the previous embodiments, closing

conductors 86a, 87a, 88a and 96a, 97a, 98a are maintained well away from the housing 38 (especially the plasma duct region) and the cathode plate 32. The closing conductors 86a, 87a, 88a and 96a, 97a, 98a may be disposed on the same side of the housing 38 as the deflecting conductors 86, 87, 88 and 96, 97, 98 of the deflecting system, for example by disposing the closing conductors 86a, 87a, 88a and 96a, 97a, 98a well above or below the level of the housing 38. Alternatively the closing conductors 86a, 87a, 88a and 96a, 97a, 98a may be disposed on the opposite side of the housing 38 but remote therefrom, in which case it is preferable that the distance S between the closing conductors and focusing conductors arranged along opposite sides of the housing (for example focusing conductors 86, 87, 88 and closing conductors 96a, 97a, 98a) ranges from 1.5 H to 3 H where H is the width (transverse) of the housing 38.

In the operation of this embodiment, as the target surface 34 evaporates the plasma is concentrated between the magnetic fields generated by the conductors 62, 64 and flows into the deflection region defined between the magnetic fields generated by deflecting conductors 86, 87, 88 and 96, 97, 98. The plasma is thereby deflected along a flow path coinciding with the asymmetrical pattern of the deflecting conductors 86, 87, 88 and 96, 97, 98 and flows toward the substrate holder 6 without contacting the housing 38. The plasma remains confined between magnetic fields and is thereby deflected away from the working axis 33 of the cathode plate 32. The neutral component continues in a generally straight direction and settles on an interior wall of the housing 38 in the vicinity of the working axis 33 of the cathode plate 32, while the plasma continues along the plasma duct into the coating chamber to the substrate holder 6.

FIG. 10a illustrates a preferred embodiment of an arc coating apparatus according to the invention, providing a pair of cathode plates 32 disposed in a cathode chamber at opposite ends of the housing 38, in communication with the substrate holder 6 through a parallelepipedal plasma duct 31. Internal linear anodes 50 configured as described above are suspended above each target surface 34, separated therefrom by a shield 54. Anodes 50 are defined herein as "internal" because they are disposed within the plasma duct, which is defined between the cathode plates 32 and the substrate holder 6.

A further internal anode, deflecting electrode 120 comprising a linear plate 122 having baffles 124, is disposed along the plasma duct 31 at the approximate center between the two cathode plates 32. The baffles increase the anodic surface area, effectively functioning as a chain of internal anodes, which provides better stabilization and steering of arc spots. They also serve to trap macroparticles emitted from the evaporation surface 34. As in the previous embodiment, the baffles 124 are oriented as much as possible parallel to the direction of the magnetic field to reduce diffusion losses. This "dividing" anode 120 also serves to repel ions and thus deflect the plasma streams toward the substrate holder 6.

In this embodiment focusing conductors 82, 84, 92 and 94 are disposed parallel to the long sides 32a, 32b of the cathode plates both about the regions in front of the cathode plates 32 and about the exit of the plasma duct 31 in the coating chamber. In between the sets of focusing conductors 82, 92 and 84, 94, deflecting conductors 86, 96 are disposed about the portion of the housing 38 where the plasma duct 31 turns toward the axis of the substrate holder 6, i.e. adjacent to a portion of the housing 38 containing the cathode plates 12, creating opposed magnetic cusps directed perpendicular to the axis of the cathode chamber, to thus deflect plasma toward the substrate holder 6. In the embodiment shown the closing conductors 82a, 84a, 86a, 92a, 94a and 96a must be disposed remote

from the plasma duct **31** in order to ensure that the cathode plates **32** are disposed only within the magnetic cusps generated by the focusing and deflecting conductors **82, 84, 92, 94** and **86, 96**, so that cathodic evaporate is drawn into the plasma duct **31** and not toward the back wall of the housing **38**. Alternatively, as in the embodiment of FIG. 9 the closing conductors **82a, 84a, 86a** and **92a, 94a, 96a** may be disposed on the opposite side of the housing **38** but remote therefrom.

The embodiment of FIG. **10a** also provides one or more external anodes **130** surrounding the substrate holder **6**. Anodes **130** are defined herein as "external" because they are disposed outside of the plasma duct **31**. Thus, the external anodes **130** do not deflect the plasma, but instead repel ions to prevent diffusion losses on the walls of the housing **38** and prolong ionization of the coating material to improve coating efficiency. Such external anodes **130** can also be provided about any desired portion of the housing **38**; Additionally the coating chamber itself, or some portion thereof, may be grounded to serve as an anode.

Further, since the housing **38** is insulated from the cathode plates **32** by dielectric spacers **39**, the housing **38** may be left at floating potential as shown in the Figures. Alternatively, providing a floating potential screen or shielding (not shown) between the cathode **32** and the housing **38** to prevent the arc from moving into a gap between the cathode **32** and the housing, will effectively turning the housing **38** into an external or surrounding anode.

The internal anodes **32, 120** and external anode **130** are preferably electrically isolated and thus each is provided with an independent power supply, which allows for better control over their independent functions.

It is also possible to differentially activate the focusing conductors **82, 84** and **92, 94** to trap the metal vapour component of the plasma within the plasma duct while allowing the electron current to flow freely through the coating chamber to the auxiliary anodes **130** surrounding the substrate holder **6**. This mode of operation is a "plasma immersed" mode, which provides a high degree of ionization and activation of the gaseous plasma environment in the coating chamber without deposition of metal cathodic arc plasma coatings. The plasma immersed mode supports several different types of plasma processes, such as fast ion cleaning, ion nitriding, ion implantation, and arc plasma-assisted low pressure CVD coating processes. For example, the first stage of a particular coating process may require ion cleaning. The cathodic arc sources **34** may be used as a powerful electron emitters, to extract electron current from the cathode to the external anode **130** surrounding the substrate holder **6**, providing a plasma immersed environment for fast ion cleaning. Argon, nitrogen, methane etc. may be injected as a plasma-created gas in conjunction with an RF generator providing a self bias potential at the substrate holder for effective ion bombardment, as illustrated by the examples.

Magnetron sputtering plasma sources **400** can be also used as primary vapor plasma sources in a large area filtered plasma source embodiment of the invention, as illustrated in FIG. **10b**. In this embodiment a magnetron magnetic field is created by a set of magnetron magnets **402, 403** attached to a magnet holding plate **401** disposed behind the cathode target plate **32**. The magnetron magnetic field must overlap and be directed in the same direction as the focusing magnetic field created by magnetic conductors **82, 84, and 92, 94**. This allows for the extraction of an increased amount of magnetron metal sputtering plasma from the magnetron discharge area toward the plasma-guide portion of the electromagnetic vapor plasma filter chamber **500**. The mixed vapor-gaseous plasma flow will be confined in a curvilinear magnetic field created

by focusing conductors **82, 84** and **92, 94** and deflecting conductors **86, 96**. In this embodiment the magnetron targets **32** are positioned in a magnetic half-cusp area on a side of plasma guide chamber **500** where the magnetic force lines converge toward the dividing anode **120**. This ensures that all vapor-gaseous plasma extracted from the magnetron discharge will be focused and directed toward the substrates to be coated on substrate holder **6**, while neutral droplets and macroparticles are removed from the plasma flow and trapped by baffles **124**.

Auxiliary arc cathodes (not shown) can be installed elsewhere in the coating apparatus, out of optical alignment from the magnetron targets **32**. For example, FIG. **10c** shows a thermionic hollow cathode **510** installed in the coating chamber, to establish an auxiliary arc discharge between the auxiliary cathode **510** and the magnetron anodes **150**. This results in an increase of the ionization rate of the magnetron discharge plasma while also increasing the ionization rate of the gaseous component of the plasma environment in the coating chamber. This provides for magnetron sputtering at lower operating pressures, and improves coating quality by increasing ionization and activation of the vapor-gaseous plasma environment while eliminating droplets, macroparticles and neutral clusters from metal-gaseous vapor plasma flow.

The filtered vapor plasma embodiment can optionally have both magnetron sources **400** and cathodic arc sources **34** as primary vapor plasma sources, as illustrated in FIG. **10b**. In this embodiment the targets **32** are provided with additional high current low voltage power supplies **46** connected to the cathode target plate **32** via switches **445** and an arc igniter **48**. On each side the magnetron high voltage low current power supply **430** is connected to the target plate **32** via switch **440**. The magnetron magnet set can preferably be moved away from the target **32** by using a shaft **410** attached to the magnet holding plate **401**.

In the operation of this embodiment in a filtered magnetron sputtering mode, argon as a sputtering gas is injected through argon inlets (not shown) in the vicinity of both magnetron target plates **32** installed at opposite sides of the filtered plasma arc source apparatus. A reactive gas (nitrogen, acetylene) can be optionally supplied into the coating chamber, for deposition of cement coatings (TiN, TiC, TiCN etc.). The switch **445** is disconnected and the arc power supply **46** is turned off. The switch **440** is activated to connect the negative pole of the magnetron power supply **430** to the target plate **32**. The magnetron plasma discharge will be largely confined by the arch-shaped magnetron magnetic field in the vicinity of the magnetron target cathode plate **32**, forming a generally rectangular plasma ring along the gap between the edge magnet set **403**, the central magnet set **402** and the end magnets (not seen in FIG. **10b** or **10c**). An erosion zone is formed by plasma sputtering on the evaporation surface of the magnetron target **32** along the path of the magnetron closed loop discharge, where the plasma density is strongest. The focusing magnetic field created by focusing conductors **82, 84** and **92, 94** will create converging magnetic field lines in front of the magnetron targets **32**, i.e. over the target surface, which will extract vapor plasma flux from the magnetron discharge and focus it toward the plasma-guide portion of the electromagnetic vapor plasma filter chamber **500**. This vapor plasma flux will be further confined into the converging magnetic half-cusp field, which will deflect it toward the coating chamber where substrates to be coated are installed on substrate holder **6**. The focusing conductors **82, 84** and **92, 94** installed at the exit of the plasma-guide will focus the vapor plasma toward the substrates to be coated. The dividing anode **122** will repel metal ions, effectively diverting the ion trajectories

toward the coating chamber. Macroparticles and neutral vapor atoms will be trapped by baffles 124, installed at the dividing anode plate 120. When the auxiliary arc discharge is activated between the thermionic cathode 510 and magnetron anodes 150, the ionization rate will be increased in the vicinity of the magnetron targets 32. That increases the productivity of magnetron sputtering, as well as reduces the operating pressure of the magnetron discharge. The electromagnetic filter of this invention has higher conductance at lower pressures due to a reduced frequency of collisions between ions and other atomic particles. This results in a higher ion flux at the filter exit, and thus higher productivity of the filtered magnetron sputtering process.

In a filtered cathodic arc evaporation mode, the switch 440 is opened to disconnect the magnetron power supply 430, and instead the switch 445 connecting the arc power supply 46 to the cathode target plate 32 is closed. When the arc power supply 46 is turned on, the arc igniter 48 will ignite the cathodic arc discharge at the evaporation surface of the cathode target plate 32. A reactive gas can optionally be supplied to the coating chamber for deposition cermet coatings. The magnetron magnets 402, 403 will be moved away from the target plate 32 area by shaft 410 supporting the magnet holding plate 401. Cathodic arc spots will be steered by magnetic conductors 82, 84 and 92, 94 parallel to the long side of the targets 32 and, independently by the coils 66, 68 parallel to the short side of the targets 32. This will provide the maximum target utilization rate and arc spot confinement to the wide erosion corridor area on the evaporation surface of the target plate 32. At the same time the steering/focusing conductors 82, 84 and 92, 94 will focus the arc vapor plasma toward the magnetic half-cusp area created by deflecting conductors 86, 96. The deflected plasma flow will be further focused by focusing conductors 82, 84 and 92, 94 installed at the exit of the plasma-guide chamber toward substrates to be coated installed on substrate holder 6. An auxiliary anode 130 can be used to improve the ionization and activation rate of the gaseous component of the vapor-gaseous flow. FIGS. 7c and 7d illustrate a further embodiment of the invention, similar to the embodiment of FIGS. 7a and 7b but providing multiple rectangular cathode targets incorporated in one rectangular cathodic arc source unit. Housing 38 contains two rectangular cathode assemblies consisting of target plates 34 attached to water-cooled target holder and vacuum arc igniters 170. Each cathode target assembly is surrounding by an insulated shield 140, which prevents cathodic arc spots from moving toward side surface of the cathode assembly. Central anode 50 can be optionally installed in front of the cathode target plate 32. The insulated shield 54 can be installed in a central area of the target plate 32, to prevent cathodic arc spots from moving toward central area of the target where the steering magnetic field component that is tangential to the plate surface 34 is not sufficient to confine arc spots within the erosion corridor 200. Two pairs of focusing magnetic coils 84 and 62 are using to steer cathodic arc spots along long sides of the targets 32, while simultaneously focusing the plasma flow toward the substrate holder 6 installed in the main vacuum chamber. Another pair of magnetic coils 66, 68 is disposed on a backside of each cathode assembly. The linear conductors 66, 68 are parallel to the short sides 32c, 32d of the cathode targets 32, providing steering of cathodic arc spots along short sides of the target surface 34. Conductors 66, 68 must be installed with opposite polarities, providing steering of cathodic arc spots in the same direction as adjacent focusing conductors 62, 84 steering cathodic arc spots along the erosion corridor 200. Surrounding anodes 150 can be optionally sectioned or partitioned, providing independent anodic cur-

rent circuits for cathodic arc spots located both near the short sides 32c or 32d of the target plate 32 (anodic pair 151-151a in the embodiment shown in FIG. 7d) and long sides 32a or 32b of the cathode target 32 (anodic pair 152-152a in the embodiment shown in FIG. 7d). This also allows for the detection of cathodic arc spots stagnating near the short sides or long sides of the target surface 34. As soon cathodic arc spots are located near either short or long side of the target surface 34 for time longer than $t_s \approx 0.1 l_s / v_s$, (where l_s is a length of a short or long side of the cathode target plate 34, v_s is a velocity of a movement of cathodic arc spots under influence of steering magnetic field), the arc current can be turned off to eliminate the arc spots, followed by re-ignition of the arc by igniters 170. Sectioning or partitioning the anodes, including both surrounding 151, 152 and central 50, allows for the optimal distribution anodic arc current to provide maximum reliability of steering of arc spots inside of erosion corridor 200.

Alternatively, instead of a shield (either a shield 140 around the cathode plate 32 or a shield 54 covering the stagnation zone in front of the evaporation surface 34), the cathode plate 32 can be surrounded by a material that has a very low cathodic arc spot sustainability, or this material can be inserted in the area of the cathode plate 32 where arc spots are stagnating. For example tungsten, molybdenum, boron nitride-based ceramics etc., can be used to prevent arc spots from moving in undesirable areas of the evaporation surface 34.

FIGS. 11 to 13 illustrate a further embodiment of the invention providing local correctional magnets 200 and 210 for guiding the arc spot between one long side 32a of the cathode plate 32 and the other long side 32b, and providing a different anode arrangement.

Short side correctional magnets 200 preferably each comprise at least one magnetic coil 202 surrounding an electromagnetic core 204, and are respectively disposed along the short sides 32c, 32d of the cathode plate 32. The core 202 concentrates the magnetic field generated by the coil 202, so that when the coil 202 is activated the arc spot is constrained to move along the arc-shaped magnetic field lines which extend over the short side 32c or 32d of the cathode plate 32.

In this embodiment long side correctional magnets 210 are also provided along both long sides 32a, 32b of the cathode plate 32, near the short sides 32c, 32d, to similarly constrain the motion of the arc spot as the arc spot nears the short sides 32c, 32d. Long side correctional magnets 210 similarly preferably each comprise at least one magnetic coil 212 surrounding an electromagnetic core 214 which concentrates the magnetic field generated by the coil 212, so that when the coil 212 is activated the arc spot is constrained to move across the magnetic field lines in a direction transversal to the arc-shaped magnetic field lines which extend over the ends of the long side 32a or 32b.

The directions of the magnetic field lines generated by the correctional magnets 200, 210 must correspond to the motion of the arc spot along the long sides 32a, 32b as determined by the steering conductors 66, 68 (shown in FIG. 11). The correctional magnets 200, 210 act on the arc spot only as it nears and traverses the short sides 32c, 32d of the cathode plate 32, to maintain an uninterrupted steering pattern about the cathode plate 32. The strength of the magnetic fields generated by the correctional magnets 200, 210 can be varied by varying the current through the coils 202, 212 or by providing additional coils (not shown) surrounding the cores 204, 214 which can be selectively activated to superimpose an additional magnetic field onto the core 204 or 214.

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In this embodiment a linear internal anode **220** comprises a series of anode blocks **222** and **230**. Interior anode blocks **222** provide an anode plate **224** and baffles **226** disposed generally orthogonally in relation to an anode plate **224**. As in the previous embodiments the anode plate **224** and baffles **226** are each oriented in a direction parallel to the direction of the plasma flow. The anode **220** further includes end anode blocks **230**, preferably comprising solid water-cooled blocks, which serve to isolate the interior regions of the anode **220** from cathodic evaporate eroded from the short sides **32c**, **32d** of the cathode plate **32**. The use of separate “blocks” helps to better distribute the arc current and reduces reliance upon a single anode body.

The anode blocks **222**, **230** are preferably independently controlled by separate power supplies **227** disposed through water-cooled anode pipes **229**, mounted to and insulated from the housing (not shown) by insulating spacers **228**. The strength of the current through an anode block **222** or **230** determines the absence or presence of an arc spot, and thus suitable software can be employed to raster or scan through the blocks **222**, **230** within the anode **220** in concert with the motion of the arc spot about the erosion zone **70**. This arrangement helps to reduce the interval during which the arc spot is passing from one long side of the cathode **32** to the other. Moreover, if the arc spot stagates at any point along the erosion corridor **70**, the power supply to an adjacent anode block **222** or **230** can be deactivated or reduced, and/or the power supply to a more remote anode block **222** or **230** can be activated or increased, to keep the arc spot in motion.

The linear focusing conductors **82** and **84** shown in FIG. **12** partially concealed by the flange **250** are respectively disposed in front of the evaporation surface along the long sides **32a**, **32b** of the cathode plate **32**. Focusing conductors **82**, **84** produce a tangential magnetic field which steers (drags) the arc spot along long sides **32a**, **32b** of the cathode plate **32**. Because they are disposed in front of the evaporation surface **34**, the focusing conductors **82**, **84** create a magnetic cusp directed toward the coating chamber **38** (similar to that indicated by the arrows FIG. **5**). The cusp configuration tends to guide arc spots toward the center of the cathode **32**, which renders the shield **54** particularly advantageous in this embodiment as it prevents the arc spot from moving into the shadow of the anode **220**, where the magnetic field lines are generally perpendicular to the evaporation surface **34** and without the shield **54** would create a stagnation zone in the center region of the cathode **32**.

In this embodiment the closing conductors **82a**, **84a** are disposed behind the evaporation surface **34** along the long sides **32a**, **32b** of the cathode plate **32** produce a magnetic field having an arch shape over the evaporation surface **34**, which balance the acute cusp-shaped magnetic field lines produced by the focusing conductors **82**, **84** and act in conjunction with the steering conductors **66**, **68** respectively disposed along the short sides **32d**, **32c** of the cathode plate **32**, along with the correctional magnets **200**, **210** which also guide arc spots along the short sides **32d**, **32c** of the cathode plate **32**, to guide arc spots in the same direction around the erosion zone **70**.

Thus, the conductive shield **54** spaced from the target evaporation surface **34**, together with a border shield **55** disposed about the periphery of the cathode plate **32**, precludes any cathode spot activity outside of the desired erosion zone **70**. In the embodiment shown an internal shield **57** is provided beneath the shield **54**, which also serves to prevent cathode spot activity in the shadow of the anode **220**.

In the embodiment of FIGS. **11** to **13** a surrounding anode **240** is provided around the evaporation surface **34**, generally

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orthogonally thereto. The surrounding anode **240**, which is disposed in front of the evaporation surface **34**, becomes a plasma-immersed anode which improves current exposure to the plasma flow and provides a more stable arc current surrounding the primary anode **220**. The apparatus of the invention will operate with either the “internal” anode **220** or the surrounding anode **240**; however, operation of the apparatus is improved by employing both anodes **220**, **240** simultaneously.

FIGS. **14a** through **14d** illustrate an embodiment of the arc-magnetron coating apparatus having the magnetic steering, focusing and deflecting aspects of the invention.

FIG. **15** illustrates an embodiment of the invention having four magnetrons **400**, each magnetically coupled with a dual rectangular filtered-arc source **34**. In the embodiment illustrated 4 dual rectangular filtered arc sources **34** are respectively magnetically coupled with 4 unbalanced rectangular magnetrons **400**. In this embodiment the magnetron sources **400** are in optical alignment with the substrates on the substrate holder **6**, as in a conventional coating process. Each dual filtered-arc source has at least two rectangular primary arc sources **34** installed at the opposite flanges of the filtered arc plasma guide chamber. The anode separator **122** divides the plasma guide chamber and provides a set of baffles **124** for trapping macroparticles, droplets and neutral atoms and clusters, generated by primary cathodic arc sources. Each rectangular cathodic arc source has focusing/steering coils installed parallel to the long side of the cathode target and back coils installed parallel to the short side of the targets **32** near end of the targets **32**. In this embodiment focusing conductors **82**, **84** and **92**, **94** focus the flow of plasma from of the filtered arc sources **34**, as described above, whereas conductors **86** near the exit of the plasma guide **31** are adjacent to both the filtered arc sources **34** and the magnetron source **400** and thus magnetically couple the magnetron source **400** with the adjacent filtered arc source **34** to simultaneously deflect the flow of plasma from both the magnetron arc source **400** and the filtered arc source **34** toward the coating chamber. As shown by the magnetic field lines in FIG. **15**, the magnetron arc sources are magnetically coupled to the filtered arc sources by the adjacent focusing conductors **86**, which focus and deflect the plasma toward the substrate holder **6**. The substrate holder **6** comprises a central substrate platform with multiple double rotation stations, and has near equal access to incoming vapor plasma fluxes from both filtered arc sources **34** and magnetron sources **400**, which simplifies the control of coating composition and architecture.

The ability to independently vary the current flowing through focusing conductors **84**, **94** on each side of the cathode **34** allows a rectangular cathode plate **32** to be used in a filtered arc arrangement, i.e. disposed out of optical alignment with the substrate holder **6**. By increasing the current through the conductors **84**, **94** on the side of the cathode **34** adjacent to the plasma duct **31** relative to the conductors **84**, **94** on the side of the cathode **34** opposite the plasma duct **31**, the plasma is deflected toward the plasma duct **31** and thus toward the substrate holder **6**. Neutral particles are not deflected, and are thus trapped in the baffles **124** of the anode divider **122**.

For example, FIG. **17a** illustrates the manner in which plasma becomes trapped under the closed-loop magnetic field lines **600** generated by the magnetron **400**. Plasma has a very low diffusivity across the magnetic field lines of the closed magnetic loops **600** of the magnetron, but a very high diffusivity along the magnetic field lines **600**. The magnetic field lines **600** effectively become like a “track” which confines the plasma flux (unlike neutral particles, shown as dashed arrows,

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which are unaffected by the magnetic field lines 600). Therefore, the magnetic field lines 602 generated by the deflecting conductors 84, which have the same transverse direction as the magnetic field lines 600 generated by the magnetron 400, draw the vapor plasma flux away from the target surface and deflect it toward the substrate holder 6.

If the deflecting conductors 84 are disposed immediately in front of the cathode plate 32, as shown in FIG. 17b, the magnetic field lines 602 in front of the conductors 84 overlap the magnetron magnetic field lines 600 and draw plasma away from the center of the magnetron 400 and toward the substrate holder 6 in a dispersed fashion. This arrangement is most suitable for coupling the magnetron 400 with a filtered arc source 34, because the deflecting magnetic field lines 602 simultaneously draw plasma from both sources and deflect it toward the coating chamber.

If the deflecting conductors 84 are disposed in front of the cathode plate 32 but spaced from the target surface, as shown in FIG. 17c, the magnetic field lines 604 rearward of the conductors 84 overlap the magnetron magnetic field lines and draw plasma toward the center of the magnetron 400 and toward the substrate holder 6, but in a much more confined linear stream. This arrangement provides a more focused deflection toward the substrate holder 6 in a filtered embodiment, but the linear stream of plasma does not conform as readily to the substrate shape (for example, inside surfaces of the substrate may not get coated in this embodiment, whereas the more dispersed magnetically deflected plasma in FIG. 17b coats a wider area more uniformly).

The ability to independently control the current through the deflecting conductors 84 is very advantageous in these embodiments. It allows much greater control over the flow of plasma, and by alternately varying the level of current through the opposed deflecting conductors 34, allows the plasma to be rastered back and forth over the substrate holder 6 to ensure a uniform coating over the substrates. This also allows for the mixing of plasmas having different metal vapor compositions, for example one type of metal vapor from the filtered cathodic arc source 34 and another type of metal vapor from the adjacent magnetron source 400, in a readily controllable manner. This is necessary for the deposition of composite materials.

In the embodiment shown in FIG. 16, the substrates to be coated are large diameter bearing races. For coating the inside surface of the race the race is loaded throughout the back flange of the dual filtered-arc source and rotated around its axis using a set of race drivers and guide idler (not shown) installed in the race drive tank appendage. This embodiment operates in the same manner as the embodiment of FIG. 15. The filtered arc source 34 is out of optical alignment from the substrate holder 6, to thereby eliminate droplets (which are neutral and therefore not deflected by the focusing and deflecting magnetic coil 84, 94) and trapped by baffles (not shown) installed in the plasma guide chamber and at the anode separator. The filtered arc source 34 is magnetically coupled with the magnetron 400; thus if the north pole of the magnetic field is located at the exit of filtered arc source then the central pole of the magnetron magnetic system has to be south (at the top butt-end). In this case magnetic field lines exiting from the filtered arc source 34 will end at the surface of the magnetron target 32. For the same reason, the direction of the current in the focusing (exit) current conductor of the filtered arc source has to be the same as the direction of the current in the adjacent focusing conductor of the adjacent magnetron.

Also, in this embodiment the substrate to be coated is a large ring and both the ID and OD surfaces of this ring are to

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be coated. Accordingly, instead of loading the substrate into the coating chamber and installing the substrate platform coaxial to the coating chamber, the substrates are loaded through a back flange of the plasma guide chamber of the filtered arc source, in vertical alignment. Thus, only the portion of the ring positioned in front of the filtered arc source opening will be subjected to coating deposition, from the primary cathodic arc sources 34 on both sides and from the magnetron sources 400 on both sides. The rest of the ring, which is disposed inside of the plasma guide chamber, is shielded and not exposed to the coating process. The substrate bearing race is rotated around its axis, providing a uniform filtered arc-magnetron coating of the ID surface. For coating the OD surface, the ring is moved forward toward the opposite filtered arc-magnetron station and coating proceeds in that position in the same manner, but from the opposite filtered arc-magnetron source.

EXAMPLE 1

Deposition of a diamond-like coating (DLC) on set of knives such as scalpels, razors, knives for cutting papers using two rectangular arc sources mounted in the dual rectangular plasma guide chamber of FIG. 10 with deposition zone 500 mm height.times. 300 mm width. The array of knives was installed on a rotating substrate platform facing the filtered arc source over the entire area of the deposition zone, with uniform rotation speed between about 10 to 20 rpm. A graphite rectangular plate evaporation target was attached to the cathode plate assembly. The current in the vertical steering conductors was set to 2000 amps, and the current in the horizontal steering conductors was set to 1300 amps. The arc current between the cathode and the primary (internal) anode plate was set to 300 amps. After igniting the arc with an impulse high voltage igniter, the arc spot began moving along an erosion corridor with an average speed ranging from 20 to 30 cm/s. About three to five cathodic arc spots subsisted simultaneously on the target surface. The current in the deflecting coils was set to 1500 amps each.

The first stage of the process involved ion cleaning. At this stage the cathodic arc sources were used as a powerful electron emitters. The deflecting conductors were turned off and electron current was extracted from the cathode to the auxiliary (external) anode surrounding the substrate platform, providing a plasma immersed environment for fast ion cleaning. Argon was injected as a plasma-created gas with pressure of about 4×10^{-2} Pa and an RF generator provided a 400 volt self bias potential at the substrate platform for effective ion bombardment.

During the deposition stage the pressure in the vacuum chamber was set to 10^{-3} Pa. The RF generator having a 13.56 MHz frequency provided a self bias potential ranging from 40 V to 60 V during deposition. The deflecting coils were turned off during deposition periodically with a duty cycle of 20 s on/5 s off to prevent overheating of the coating. The time of deposition was 20 minutes. The thickness of the coating, as measured by micro cross section, ranged from 0.3 to 0.35 mkm which corresponds to a deposition rate of about 1 mkm/hr with a uniformity of $\pm .10\%$.

EXAMPLE 2

Deposition of graphite coating on molybdenum glass for using as a substrate for flat panel display using rectangular molybdenum glass plates with dimensions 400 mm height.times.200 mm width.times.3 mm thick installed vertically on the rotating substrate platform. Each glass plate was

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attached to a metal plate-holder and a self bias of about 150 V was applied to the substrate platform using an RF generator with a 13.56 MD frequency. The dual filtered cathodic arc source of FIG. 10 was provided with one aluminum target evaporation surface and one graphite target evaporation surface. The pressure during coating deposition was maintained at about 10^{-3} Pa. The temperature during deposition of the graphite coating was about 400° C., provided by an array of radiative electrical heaters.

In the first stage the arc was ignited on the aluminum target, providing an aluminum sublayer with thickness about 50 nm. In the second stage a graphite coating with thickness about 150 nm was deposited over the aluminum sublayer during a coating interval of 30 minutes.

EXAMPLE 3

Deposition of TiAlN coatings on an array of hobs and end mills. The array of hobs and end mills was installed on substrate platform facing the filtered arc source exit over the entire area of the deposition zone, the substrate platform having a double (satellite) rotation with platform rotation speed 12 rpm. The dual rectangular filtered arc source of FIG. 10 was provided with an aluminum target evaporation surface mounted to one cathode and a titanium target evaporation surface mounted to the second cathode, for deposition of the TiAlN coating. The current for the titanium target was set at about 150 amps while current for the aluminum target was set at about 60 amps.

In the first stage the current of the auxiliary (external) anode was set at about 70 amps, providing a high density gaseous plasma immersed environment during both fast ion cleaning and coating deposition. The self bias potential of substrate platform provided by a RF 13.56 MHz generator was maintained at about 400 volts during ion cleaning in argon, and at about 40 volts during deposition of TiAlN coating in nitrogen. The time for ion cleaning was 5 minutes, and for deposition was about 2 hours. The argon pressure during ion cleaning was set at 6×10^{-2} Pa of argon, and for the deposition stage it was set at 2×10^{-2} Pa of nitrogen. The deposition rate for TiAlN coating for double rotated hobs and end mills was found to be about 1-1.5 .mu.m/hr.

EXAMPLE 4

Deposition of multi-layer coatings on dies and molds. An array of forging dies and extrusion molds was installed on the substrate platform with uniform rotation speed 20 rpm facing the filtered arc source exit in the dual rectangular filtered arc source of FIG. 10, for the deposition of Ti/TiN multi-layer coating with thickness ratio 0.05 mn of Ti and 0.3 .mu.m of TiN. Before deposition of the coatings fast ion cleaning and arc plasma immersed ion nitriding was performed to provide gradually increased hardness of near surface layer in a transition zone between bulk material of coating parts and the coating layer. The thickness of nitriding layer was about 40 .mu.m, provided by an auxiliary arc discharge with the current of auxiliary (external) anode set at about 90 amps and a pressure of nitrogen set at about 6×10^{-2} Pa. The number of coating layers was 11 with total thickness about 3.5 .mu.m. The current of the auxiliary anode during the deposition stage was set at about 120 amps, providing maximum total current at both titanium targets of about 500 amps. The DC bias during the ion cleaning/ion nitriding stage was set at about 200 volts, and during the deposition stage the voltage was

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reduced to 40 volts. The temperature of substrates was maintained at about 400° C. during all stages of the vacuum plasma treatment cycle.

EXAMPLE 5

Filtered magnetron deposition of cubic boron nitride (cBN) coatings. The coating system shown in FIG. 10c is used for deposition of predominantly cubic boron nitride coatings. Magnetron targets made of B_4C are used for deposition cBN coating. The rectangular magnetron erosion area was 320×80 mm². The carbide inserts are installed on substrate holder 6. The thermionic cathode ionizer 510 is activated to ionize and activate the plasma environment during an ion cleaning stage. The high current low voltage thermionic auxiliary arc power supply 46 is connected between thermionic hollow cathode 510 installed in the coating chamber and magnetron anodes 150. This also allows for an increase in the ionization rate of the magnetron plasma discharge and reduction of the magnetron operating pressure. The thermionic arc current is set to 80 amperes per each magnetron anode 150. The argon pressure in a coating chamber is set to 1 mtorr during the ion cleaning stage. The bias voltage is set to 250 volts during the ion cleaning stage. The ion cleaning stage lasts 30 minutes, during which the substrate temperature is set to 200° C. During the ion cleaning stage the deflecting and focusing magnetic fields of the filtered plasma source are not activated. The magnetron discharge is activated by closing magnetron switches 440 to turn on the magnetron power supplies 430. The magnetron current ranges between 2 and 4 amperes. The total gas pressure is increased to 2 mTorr pressure for a gas composition consisting of 20% nitrogen in argon. The magnetron discharge voltage is 600 V in this pressure range. After the ion cleaning stage the deflecting and focusing coils of the filtered plasma source are activated, the bias voltage is reduced to 80 volts and the deposition process allowed to continue for 10 hours. The thickness of the cBN coating is measured by CALO test. The hardness of the cBN coating is measured by Knoop microhardness testing equipment at 1 g load. The thickness of the cBN coating is found to be 0.2 ± 0.03 μm. The Knoop microhardness of the coating is found to be 55 Gpa+/-5 Gpa

EXAMPLE 6

TiN/TiBC two-segment multilayer composite coating. The coating system shown in FIG. 15 is used for the deposition of a two-segment TiN—TiBC multilayer composite coating on the ID and OD surfaces of a steel ring substrate. The first segment of the coating adjacent to the substrate consists of multilayer TiN/Ti coating deposited by a rectangular filtered arc source having both primary rectangular cathodic arc sources equipped with titanium targets. The upper segment consisting of a TiBC cermet composition is made by co-deposition of titanium from the filtered arc source and boron carbide from both magnetron sources having B_4C targets. For coating the ID surface of the ring, the substrate steel ring is loaded through the back flange of the rectangular filtered arc source in such a way that only a portion of the ring located in front of the filtered arc source exit is exposed to the plasma flow. The rest of the ring is shielded and not exposed to the coating deposition process. The ring is rotated around its axis providing uniform coverage of the entire ID surface. For deposition of the multilayer TiN/Ti segment, after pre-heating to 350° C. and argon ion cleaning at 250V bias and pressure 0.1 Pa, the substrate bias is increased to 1000V and the substrate is treated by titanium ion bombardment for 5

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minutes to ensure high coating adhesion. After this stage the argon pressure is reduced to 3×10^{-2} Pa, the bias voltage is reduced to 40 volts and the Ti bond layer is deposited for 5 minutes. After this stage the argon is replaced by nitrogen and the TiN layer is deposited for 25 minutes. The 10 TiN/Ti bilayers are deposited in a similar manner for 5 hours. In the next stage, methane as the second reactive gas is gradually added to the gas mixture to a 40% concentration. The deposition of the titanium carbonitride interlayer lasted for a further 1 hour. In the next stage, argon as sputtering gas is supplied near the magnetron sources. The magnetron sources are turned on and the argon pressure set to 2×10^{-1} Pa, which provides a magnetron voltage in the range between 550 and 600 volts. The magnetron currents are set at 3 amperes each resulting in power density of ~ 5.4 W/cm². The substrate temperature provided by the heater array is reduced to 200° C. and 5% of acetylene as a reactive gas is added to the argon. The rectangular filtered arc source continue to work in conjunction with the magnetrons for deposition of the TiBC upper segment composite coating for 5 hours. The resulting dual segment TiN/TiBC coating is found to have the high adhesion (upper critical load >80 N) and a coefficient of friction less than 0.3 against high speed steel. Variations of this type of coatings having high corrosion resistance are obtained by using TiCr or TiZr alloys as targets for the primary cathodic arc sources of the rectangular filtered arc source. For coating the OD surface of the ring, the substrate ring is moved ahead toward the opposite filtered arc-magnetron coating station and coating deposition of the OD surface of the ring is effected using the same coating process as described above for the ID surface.

Preferred embodiments of the invention having been thus described by way of example, modifications and adaptations will be apparent to those skilled in the art. The invention includes all such modifications and adaptations as fall within the scope of the appended claims.

The invention claimed is:

1. An apparatus for sputtering comprising:

at least one magnetron including:

- at least one rectangular cathode plate having a sputtering surface and opposing long sides and being connected to a negative pole of a current source for generating vapor at the sputtering surface, and
- a magnetic system disposed behind and in vicinity of the sputtering surface for guiding the vapor along a working axis of the at least one rectangular cathode plate;
- a coating chamber including a substrate holder for holding a substrate to be coated by the apparatus;
- a plasma duct having (a) an entrance disposed along the working axis and (b) an exit disposed off of the working axis, such that the coating chamber is in communication with the at least one rectangular cathode plate through the exit, the plasma duct, and the entrance;
- at least one anode spaced from the sputtering surface and disposed between the sputtering surface and the entrance, the at least one anode being connected to a positive pole of another current source;
- at least one cathode-ionizer, disposed outside the exit and connected to a negative pole of the another current source, for generating an arc-discharge through the plasma duct between the at least one cathode-ionizer and the at least one anode so as to ionize the vapor to create a magnetron vapor plasma; and
- a plurality of deflecting conductors arranged around the plasma duct and defining a curvilinear path, for deflecting flow of the magnetron vapor plasma through the

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- plasma duct, off of the working axis, and through the exit toward the coating chamber.
- 2. The apparatus of claim 1, the at least one cathode-ionizer being out of optical alignment with said at least one anode.
- 3. The apparatus of claim 2, the at least one cathode-ionizer being contained within said coating chamber.
- 4. The apparatus of claim 1, the plasma duct being generally curvilinear.
- 5. The apparatus of claim 1, said anode being a grid disposed in front of said target surface.
- 6. The apparatus of claim 1, further comprising a plurality of focusing conductors for focusing the magnetron vapor plasma.
- 7. A method of controlling a flow of plasma in a sputtering apparatus, comprising:
 - using a magnetron to create, by sputtering a sputtering surface of a rectangular cathode plate of the magnetron, a vapor along a working axis of the magnetron;
 - generating an arc-discharge through a plasma duct between a cathode-ionizer and an anode to ionize the vapor to create a magnetron vapor plasma, the plasma duct having (a) an entrance disposed along the working axis and (b) an exit disposed off of the working axis, the anode being disposed between the target surface and the entrance, the cathode ionizer being disposed outside the exit; and
 - applying a current to a plurality of deflecting conductors, arranged around the plasma duct and defining a curvilinear path from the entrance through the plasma duct to the exit, to deflect the magnetron vapor plasma to a coating chamber disposed at the exit so as to coat a substrate located in the coating chamber with the magnetron vapor plasma.
- 8. The method of claim 7, the step of generating, the cathode-ionizer being out of optical alignment with said anode.
- 9. The method of claim 8, in the step of generating, said cathode-ionizer being contained within said coating chamber.
- 10. The method of claim 7, the plasma duct being generally curvilinear.
- 11. The method of claim 7, the step of using a magnetron comprising using a magnetic system disposed behind and in vicinity of the sputtering surface to generate the vapor.
- 12. The method of claim 11, the step of using a magnetron further comprising passing current through current conductors of the magnetic system, the current conductors being parallel to opposing long sides of the rectangular cathode plate to create a magnetic field for guiding the vapor from the sputtering surface.
- 13. An apparatus for sputtering, comprising:
 - a magnetron for generating, by sputtering, a vapor along a working axis of a cathode plate;
 - a plasma duct having (a) an entrance coinciding with the working axis and (b) an exit off of the working axis;
 - a coating chamber coupled with the plasma duct at the exit and including a substrate holder for holding a substrate to be coated by a magnetron vapor plasma produced by ionization of the vapor;
 - an anode disposed between a sputtering surface and the entrance;
 - a cathode-ionizer, disposed in the coating chamber, for cooperating with the anode to generate an arc-discharge through the plasma duct to the working axis to produce said ionization; and
 - a plurality of deflecting conductors for deflecting flow of magnetron vapor plasma through the plasma duct, off of the working axis, and toward the coating chamber.

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14. The apparatus of claim 13, the plurality of deflecting conductors being configured to generate a magnetic field that defines a curvilinear path for the flow of the magnetron vapor plasma through the plasma duct to the coating chamber.

15. The apparatus of claim 14, the plasma duct comprising baffles for trapping a non-ionized portion of the vapor not following the curvilinear path.

16. The apparatus of claim 15, the baffles being mounted on a second anode that repels metal ions of the magnetron vapor plasma.

17. The apparatus of claim 13, the deflecting conductors, the cathode-ionizer, and the anode being cooperatively configured to overlap the arc-discharge with flow of the vapor along the working axis to facilitate said ionization.

18. The apparatus of claim 13, the cathode plate comprising:
the sputtering surface from which the vapor is sputtered; and

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current conductors for generating a magnetic field to guide vapor generated at the sputtering surface.

19. The apparatus of claim 13, the anode being electrically coupled with the cathode plate to also function as anode for the magnetron.

20. The apparatus of claim 13, further comprising focusing conductors for generating a magnetic field to focus a portion of the magnetron vapor plasma generated between the cathode plate and the entrance and guide the portion to the entrance.

21. The apparatus of claim 13, further comprising at least one additional magnetron for generating a metal vapor plasma, the at least one additional magnetron being located adjacent to the plasma duct and being coupled with a magnetic field generated by the deflecting conductors for directing the metal vapor plasma to the substrate by the magnetic field.

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